Precision radiation detectors for cutting edge research projects developed at the MPS Semiconductor Lab

Jelena Ninkovic

- MPS Semiconductor Lab
- Devices & Selected Applications

MPS Semiconductor Laboratory (in German: MPG Halbleiterlabor - HLL)

Located in the south-east of Munich on the Siemens Campus in Neuperlach
30 employees: scientists, engineers and technicians
+ guest scientists, engineers and students

MPG HLL is the only lab worldwide doing fully depleted silicon radiation sensors with integrated electronics optimized for different scientific projects

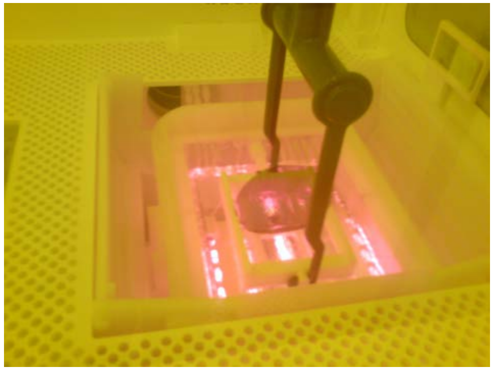
The MPG HLL history

- Started 1983 – NA11 experiment
- 6 inch process line from 2001
- Till 2013 joined lab of the MPI for Physics
  MPI for Extraterrestrial Physics
- From 2013 - Central Unit of the Max-Planck-Society
  - Open to all Max Planck Institutes
  - and to External partners

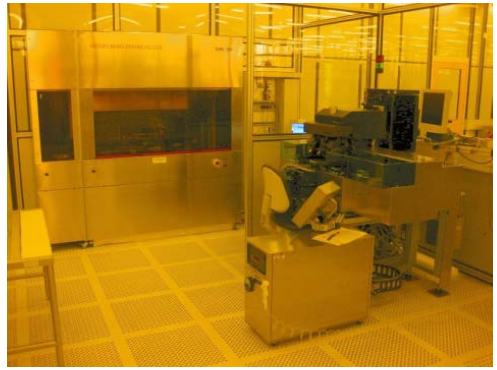
Technology - Devices - Projects

Inside HLL – Sensor Fabrication

cleaning



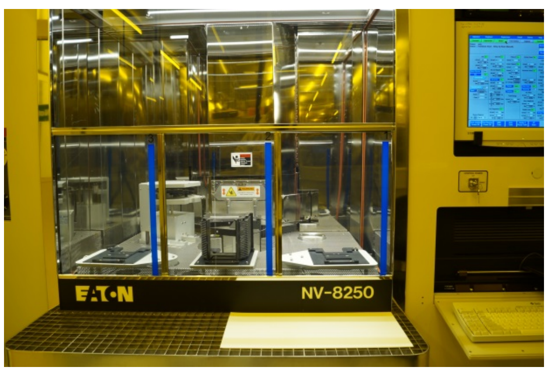
lithography



thermal

inspection

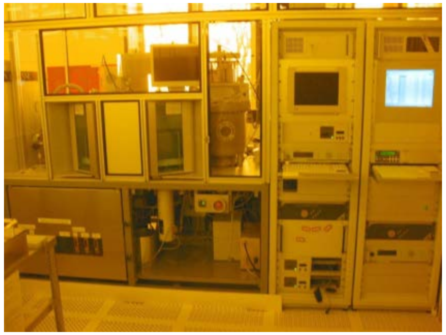
implantation



6” Si full processing line
class 1000 to class 1 in certain areas

Inside HLL – Sensor Fabrication

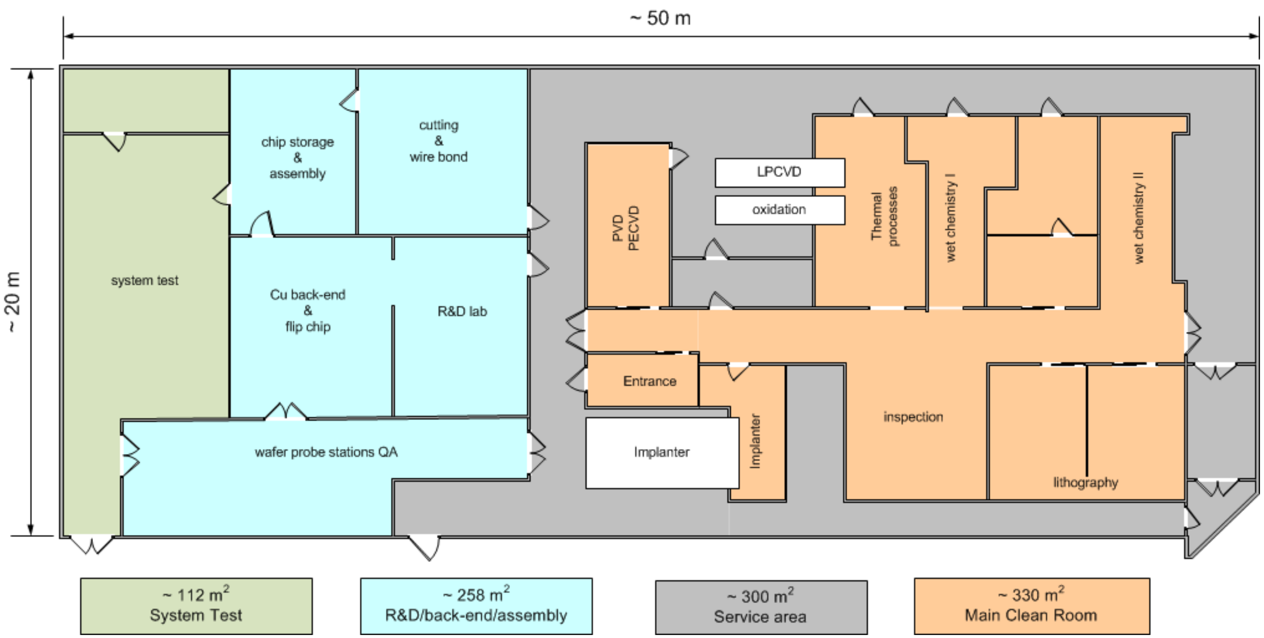
plasma and sputter



Cu line

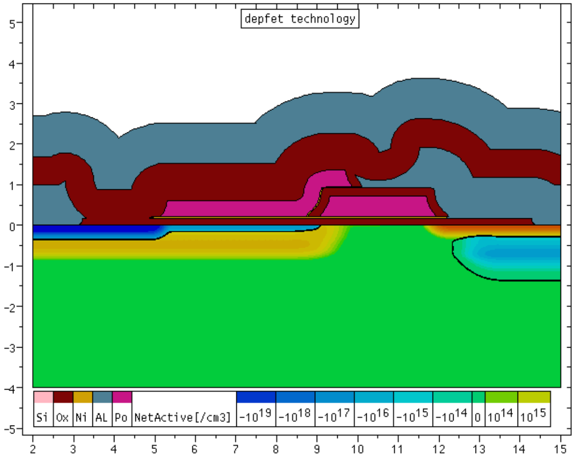
flip chip

assembly and test



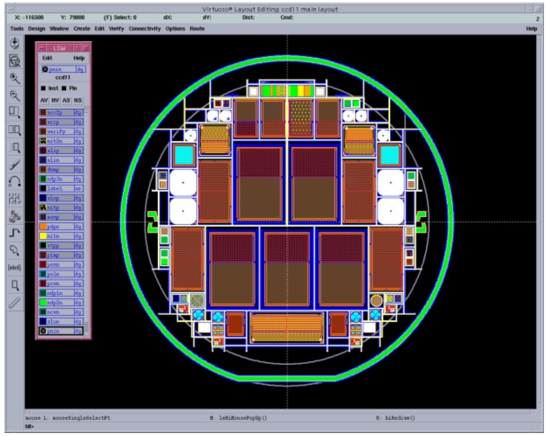
Inside HLL – Sensors and Systems: Design & Test

Process simulation



Device simulation, 2D and 3D

State-of-the-art layout tools



Wire bonding, hybrid assembly

@ HLL:

- sensor design and fabrication
- interconnection
- system/camera design and test

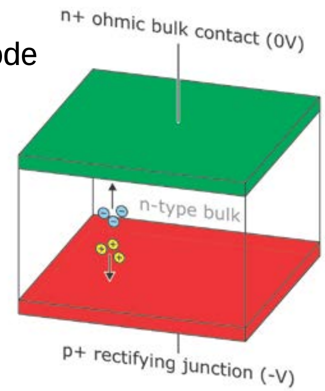
System test facilities

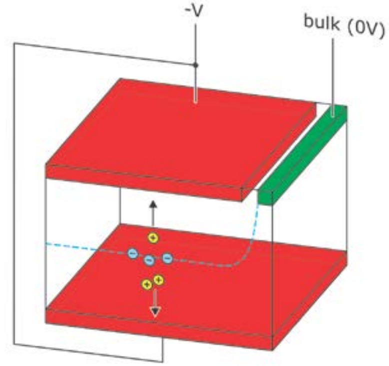
Goal : High SNR

- **Decrease noise**

Sideward depletion structure

Diode



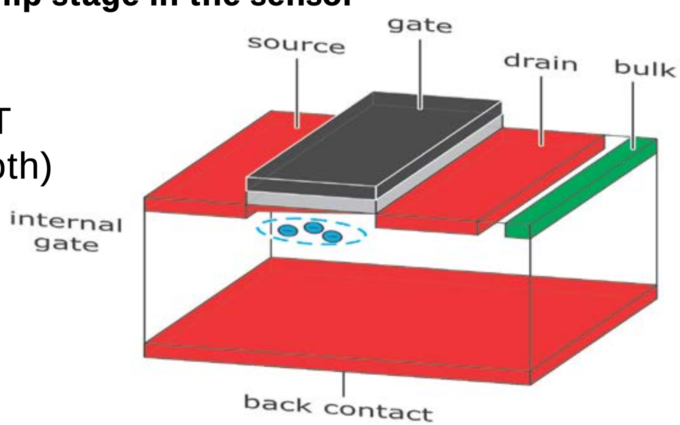


$$ENC = \sqrt{\alpha \frac{2kT}{g_m} C_{tot}^2 A_1 \frac{1}{\tau} + 2\pi a_f C_{tot}^2 A_2 + q I_L A_3 \tau}$$

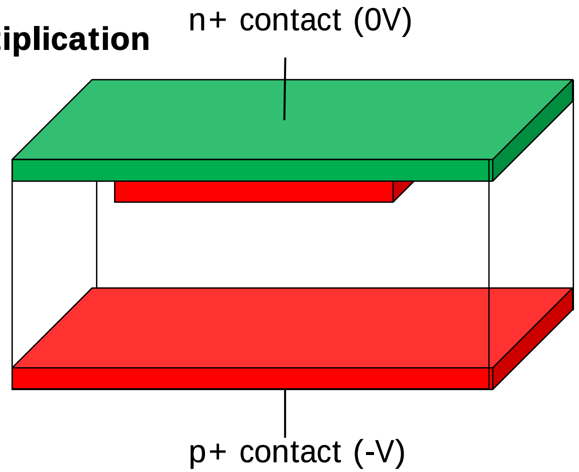
- **Amplify signal**

First Amp stage in the sensor

DEPFET
(has both)



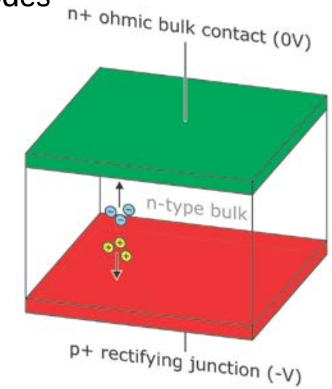
Avalanche maltiplication



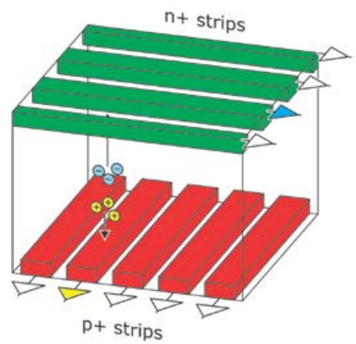
Devices @ HLL

- **Building blocks**

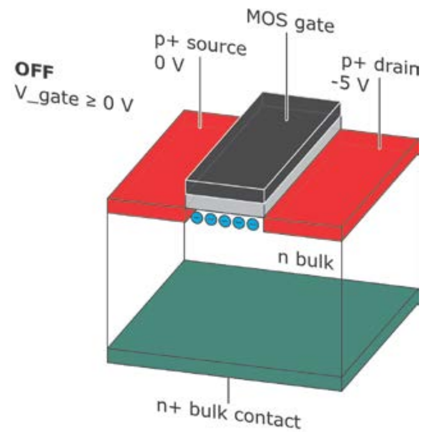
Diodes



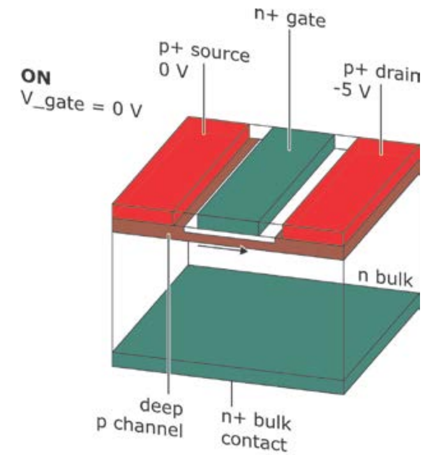
Strip detectors



MOSFETs

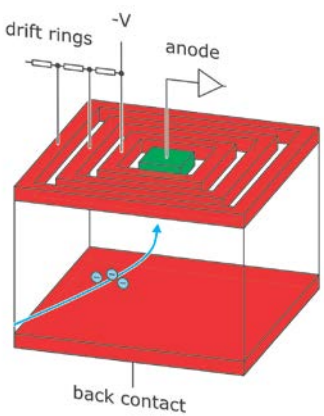


JFETs

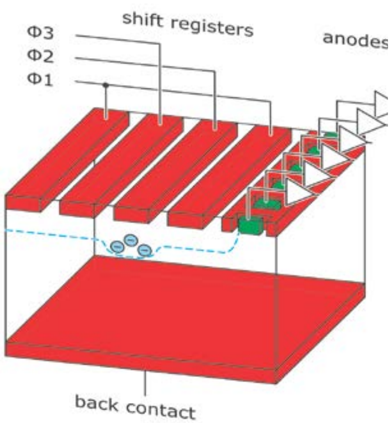


- **Devices**

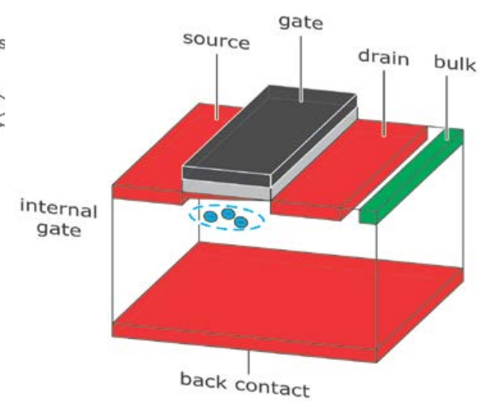
Silicon drift detectors (SDD)



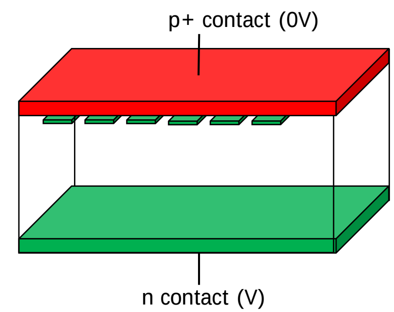
pnCCDs



DEPFETs



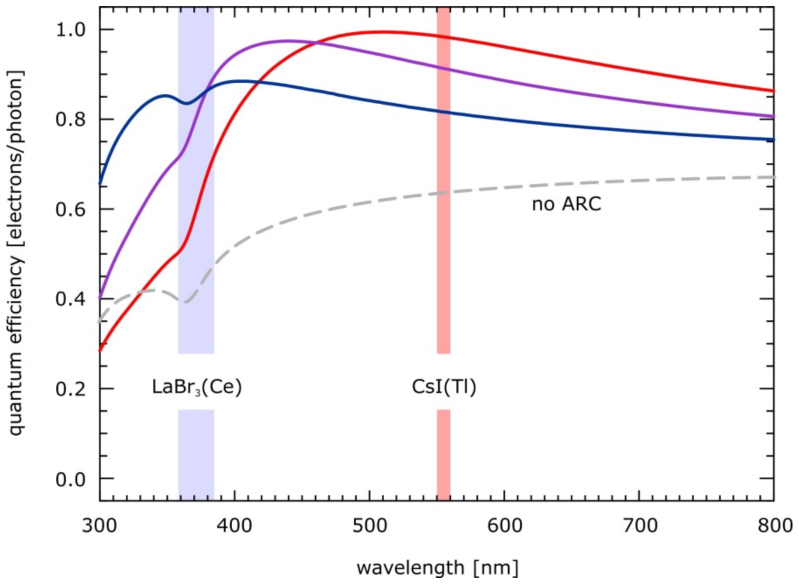
SiMPl

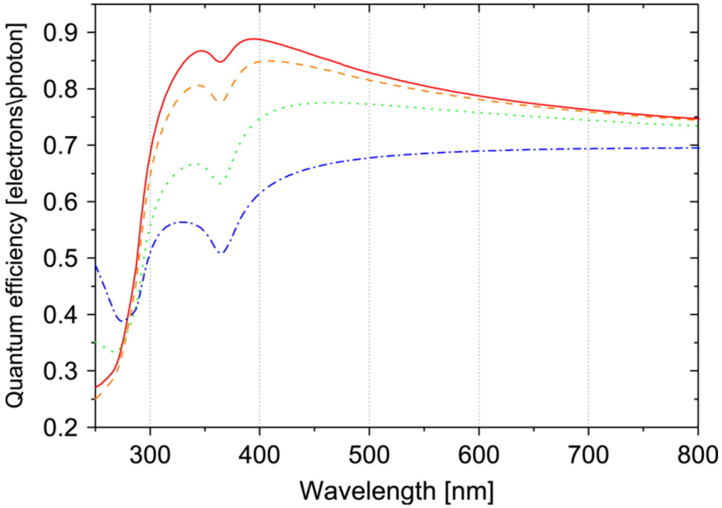


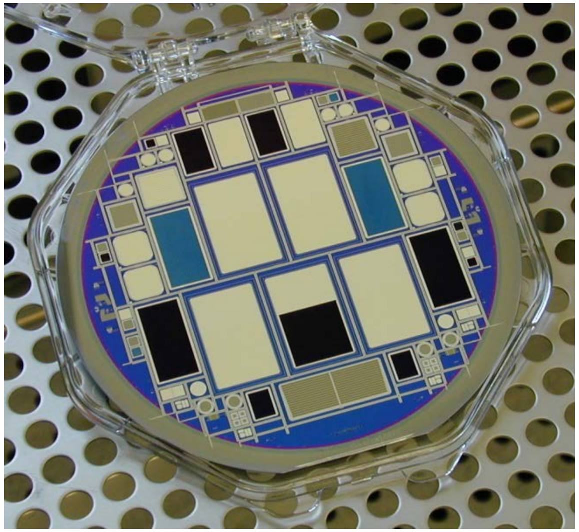
Entrance window engineering – application optimization

- anti-reflective coating (ARC)
  - ▷ sequence of dielectric layers deposited on the entrance window
  - ▷ variation of material and thickness
  - ▷ transmittance tuning to application needs

- polymer passivation
  - ▷ mechanical protection
  - ▷ optical coupling



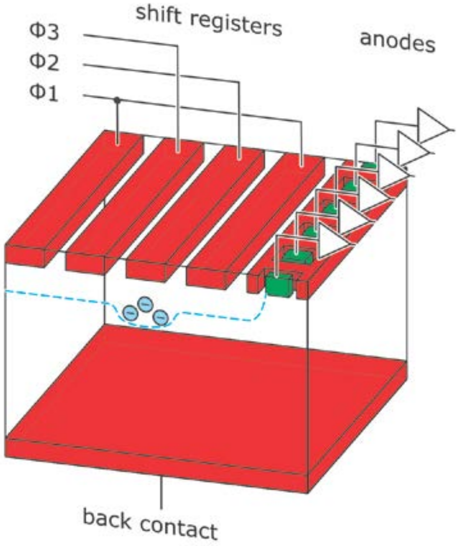




pnCCDs

Proposed by Lothar Strüder et al., 1987

- ▷ definition of potential pockets by differently reverse-biased diodes
- ▷ charge transport by periodic clocking of shift registers
- ▷ **column-parallel readout** → high frame rate (5 msec @ 200 pixel)
- ▷ integrated 1st FET (1 / column) → **low noise** (**3el. ENC**)
- ▷ backside illuminated, **fully depleted** → **high quantum efficiency**



- format ~ cm² ... **wafer scale**
- thickness 450 µm
- **pixel size 36 ... 150 µm**

Applications

- X-ray imaging & spectroscopy
- optical light imaging

Projects using pnCCDs developed and fabricated @ MPG HLL

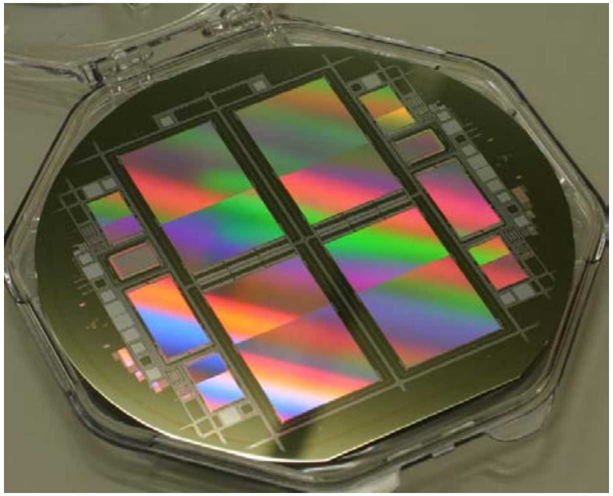
- X-ray imaging spectroscopy in space – eROSITA
- Solar Polarimetery - Fast Solar Polarimeter
- Synchrotron radiation detection – sensors for FELs

pnCCDs for eROSITA

„ extended ROentgen Survey with an Imaging Telescope Array “

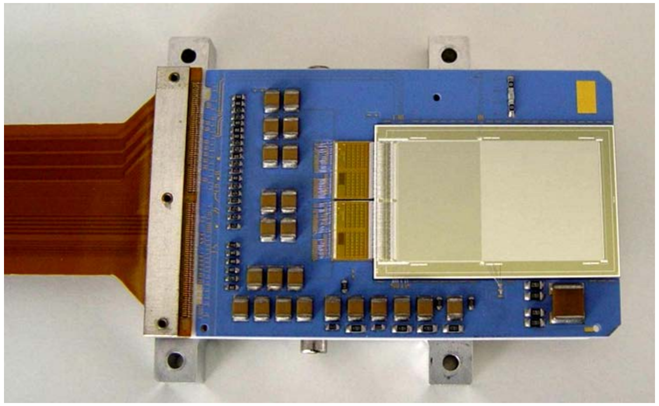
The main scientific goals are:

- map out the large scale structure in the Universe for the study of cosmic structure evolution
- Black Holes in nearby galaxies and many (up to 3 Million) new, distant active galactic nuclei and
- physics of galactic X-ray source populations, like pre-main sequence stars, supernova remnants and X-ray binaries.



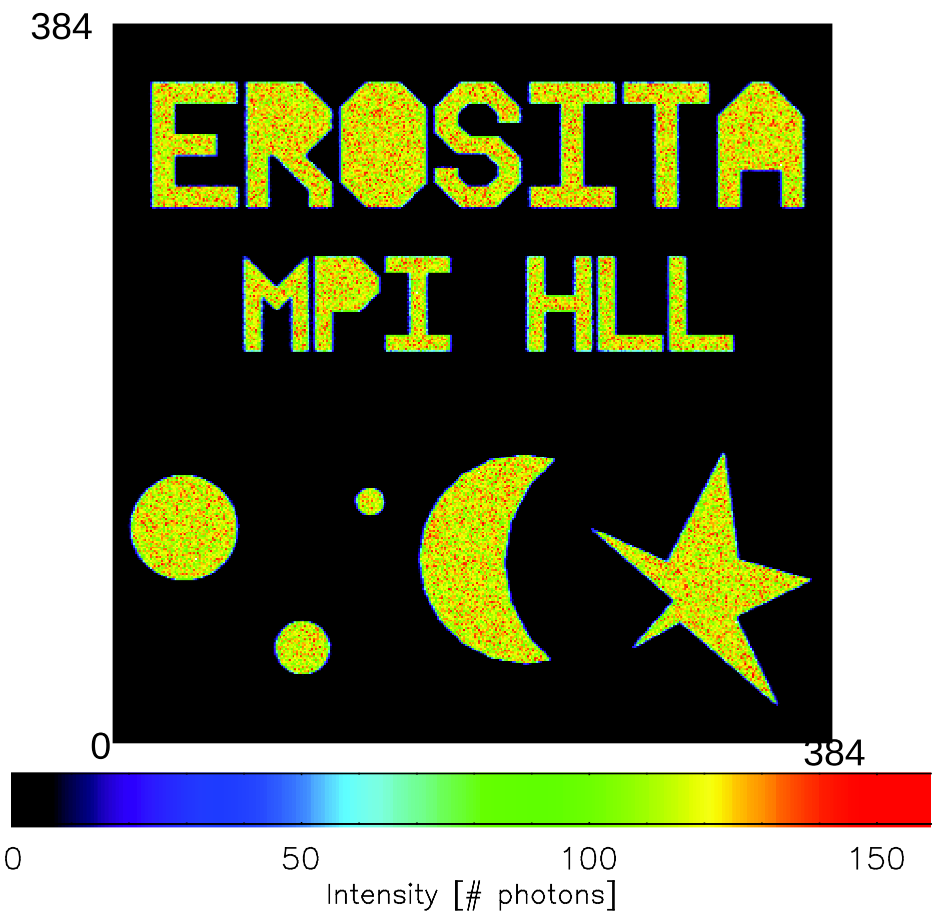
3cm x 3cm pnCCDs still on Si-Wafer.
The pn CCDs have 384 × 384 pixels in both image and frame store area.

Pixel size: 75 x 75 µm².
Frame time: 50 msec

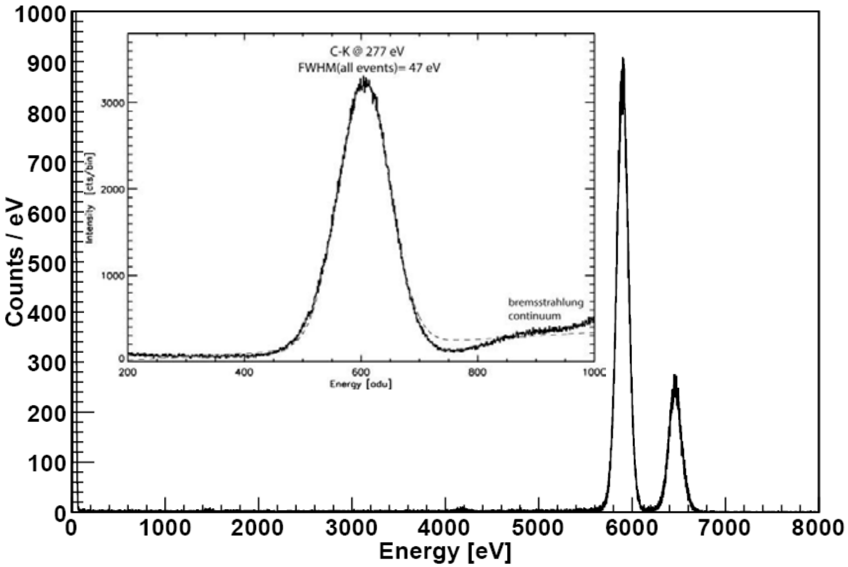


(collaboration partner MP Extraterrestrial Physics)

eROSITA pnCCD-Module



Shadow image of a 450 µm thick silicon baffle with an ^{55}Fe source mounted directly in front of the sensor



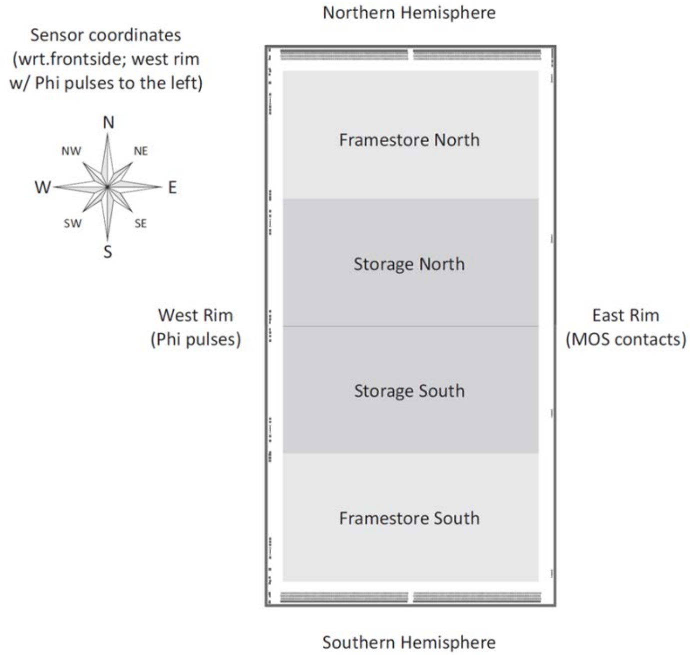
Measurements at C Ka (277eV) and Mn Ka (5,9 keV) on flight- CCDs (2cm × 2cm) show the expected energy resolution and low energy response.

Small pixel pnCCD @ HLL

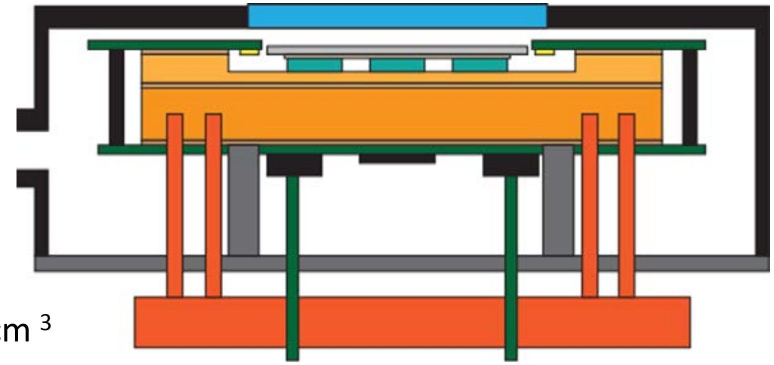
Motivation: development of a sensor for Fast Solar polarimetry
(collaboration partner MP Solar System Research)

Device characteristics:

- pnCCD concept:
  - Backside illuminated,
  - frame store,
  - split frame,
  - column-parallel readout
- Format: **1k x 1k** storage, 2 x 1 k x 0.5 k framestore
- Pixel size: **36 x 36** μm²
- Total sensitive area: 36.8 x 73.3 mm²
- Total chip size: 4.2 x 8.1 cm²
- Optimized for **optical wavelength** using ARC
- Operating temperature: -35°C (target)
- Target operating frame rate: **400 Hz** (~4 μs /row)
- Data rate: 840 Mbyte / s (16 bit)



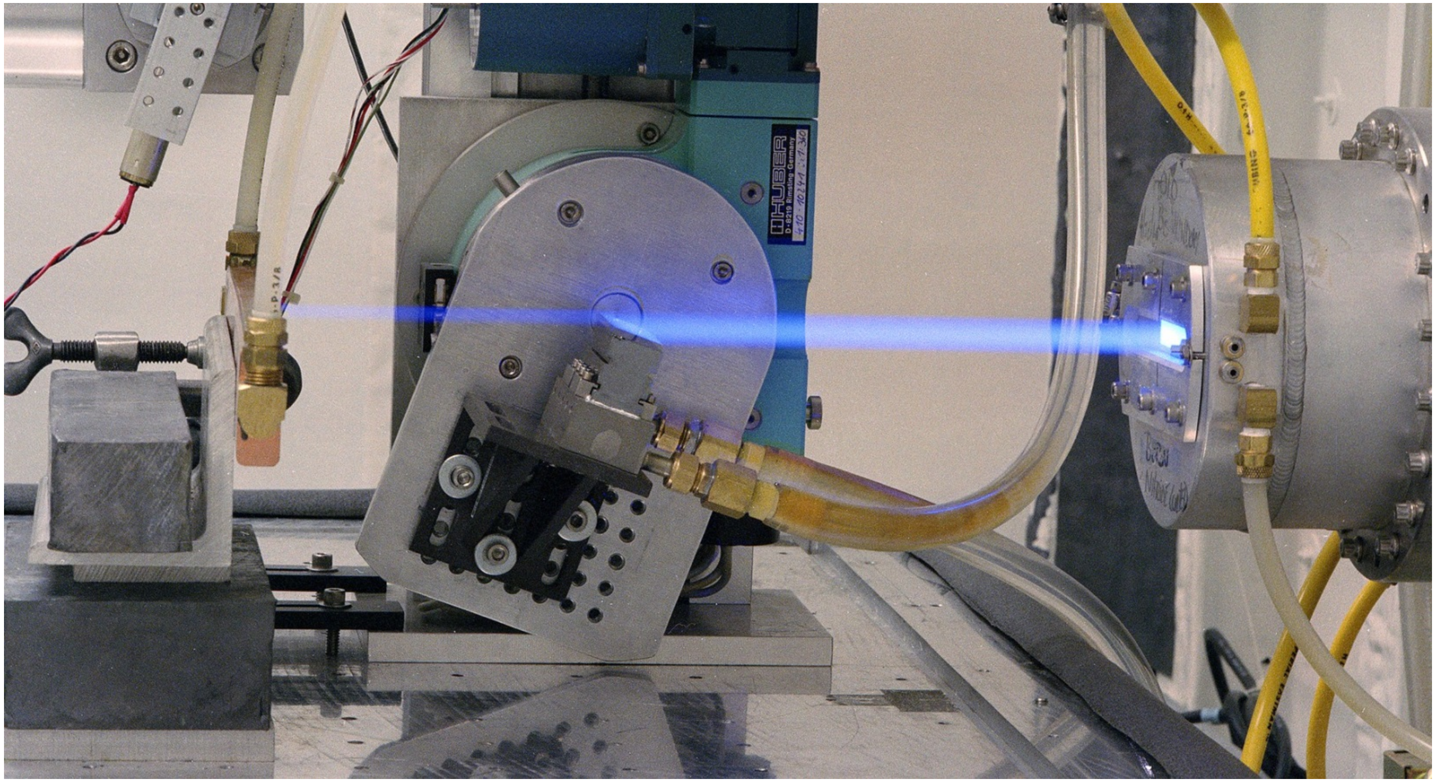
Frame store, split frame, column parallel readout pnCCD



Compact vacuum-tight camera housing ~ 18 x 25 x 10cm ³

FEL radiation detection

- Sensors for LCLS (collaboration partner MP Extraterrestrial Physics)



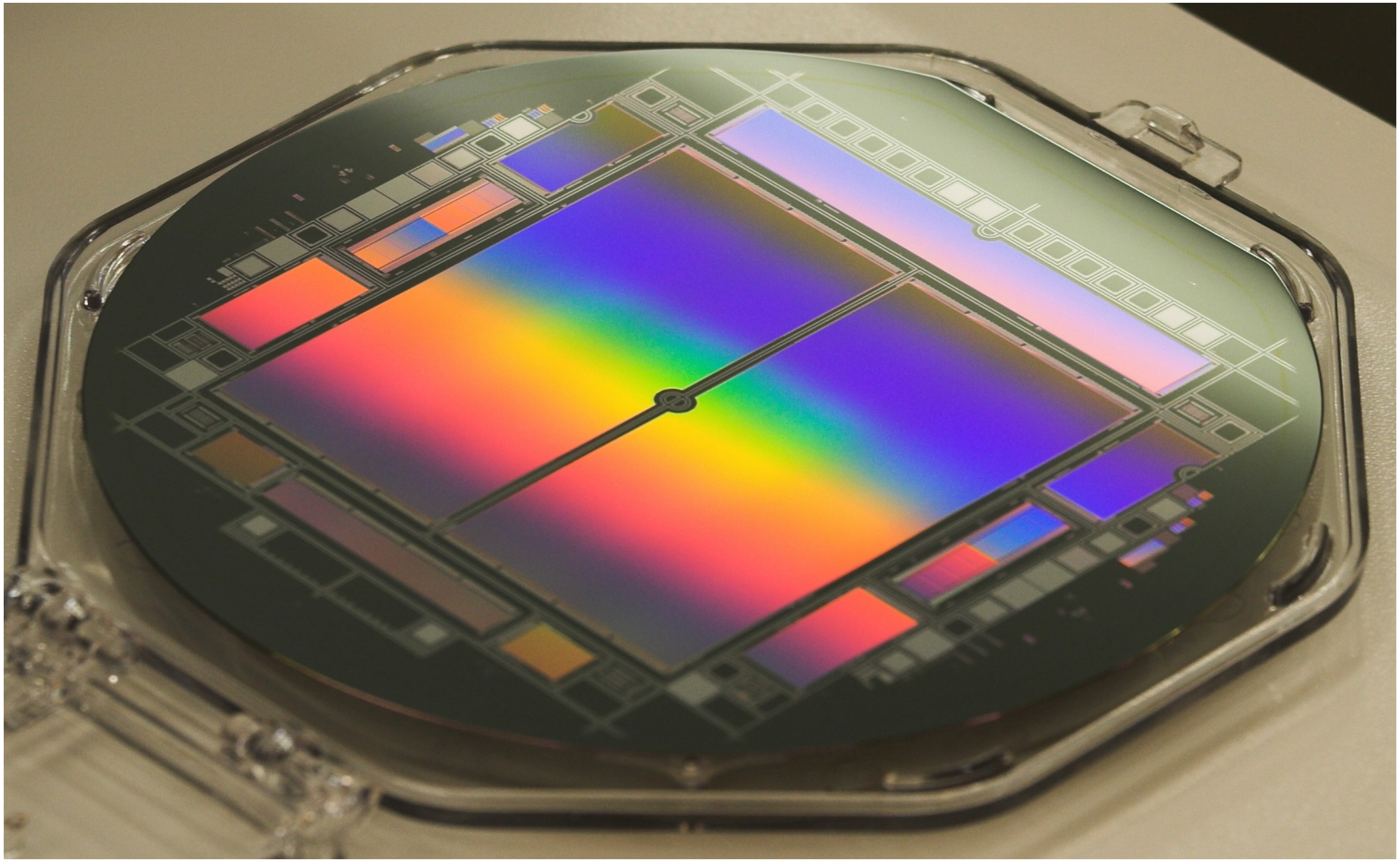
Synchrotron light from the National Synchrotron Light Source (NSLS), Brookhaven

Requirements in FEL radiation applications

Requirements of the LCLS

	LCLS	pnCCD
single photon resolution	yes	yes
energy range	0.05 < E < 24 (keV)	0.05 < E < 25 [keV]
pixel size (μm)	100	75 (150)
sig.rate / pixel / bunch	10^3 (10^5)	10^4
quantum efficiency	> 0.8	> 0.8 from 0.3 to 12 keV
number of pixels	512 x 512 (min.)	1024 x 1024
frame rate / repetition rate	10 Hz - 120 Hz	up to 250 Hz
Readout noise	< 150 e^- (rms)	< 30 e^- (rms) (2 e^- possible)
cooling	possible	- 20° C optimum room temperature possible
vacuum compatibility	yes	yes
preprocessing	no (yes) ?	possible upon request

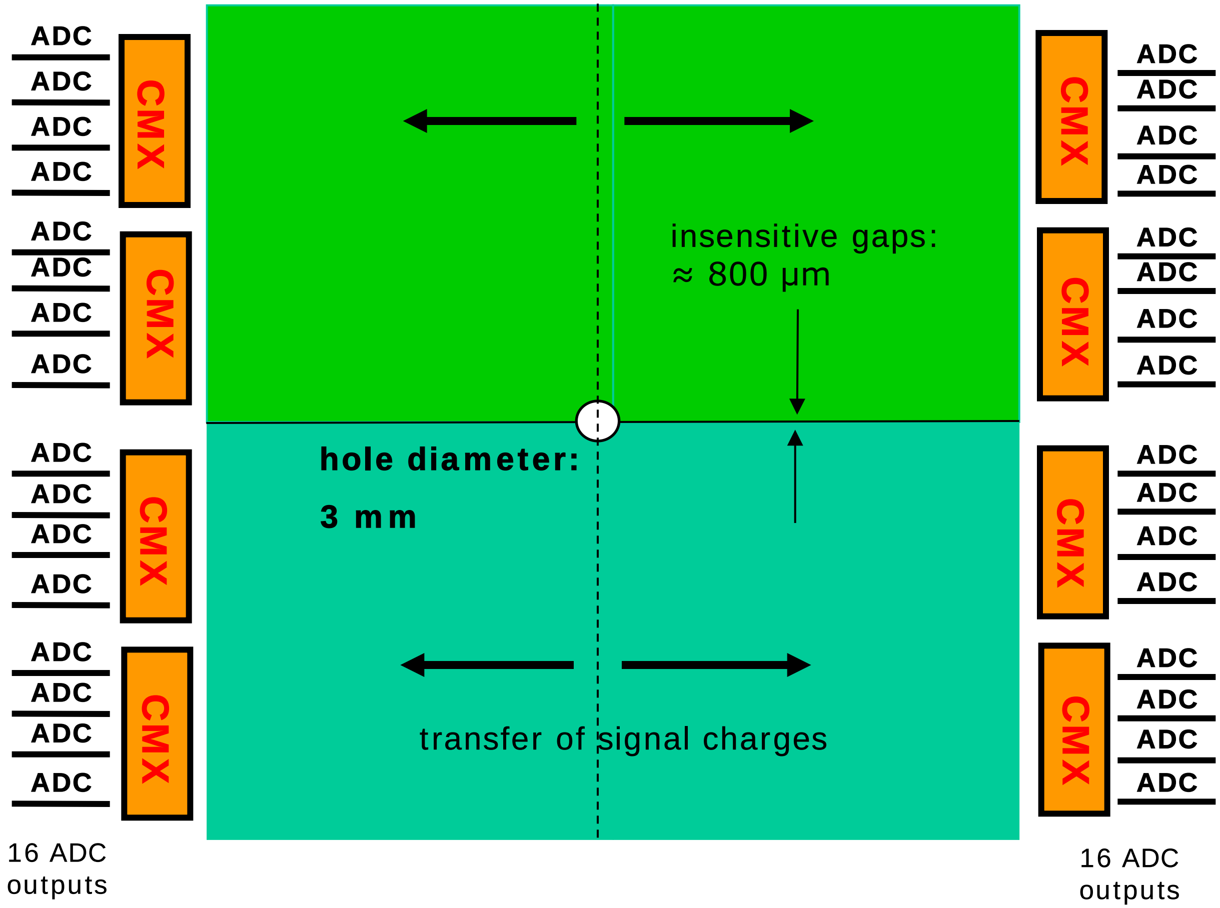
Large area pnCCDs



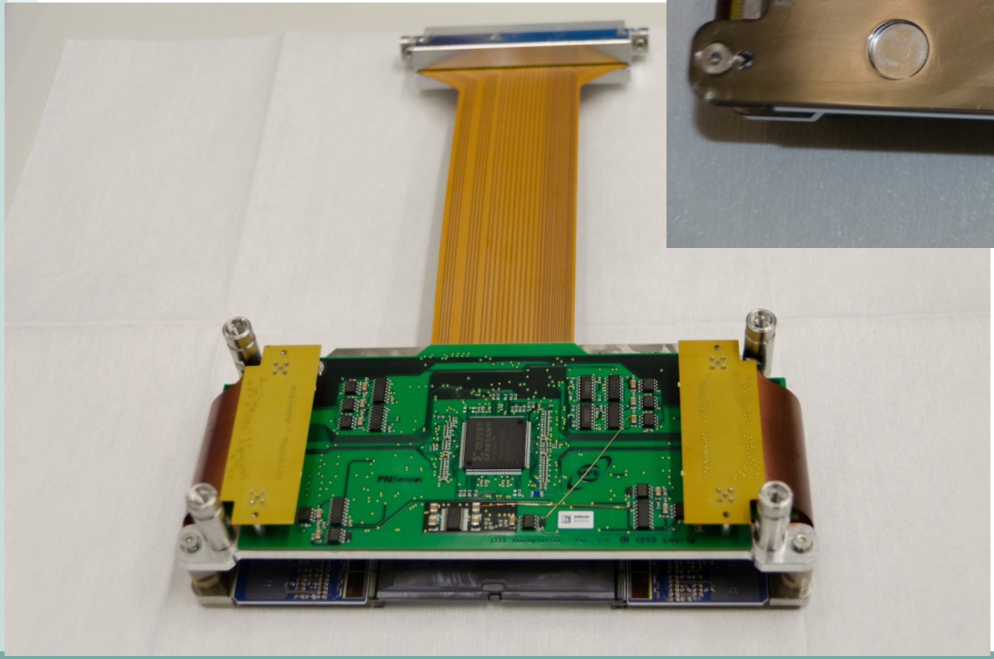
- Large area pnCCDs: 30 cm^2
- 1024 x 512 pixel of 75 x 75 μm^2
- 3.7 x 7.8 cm^2

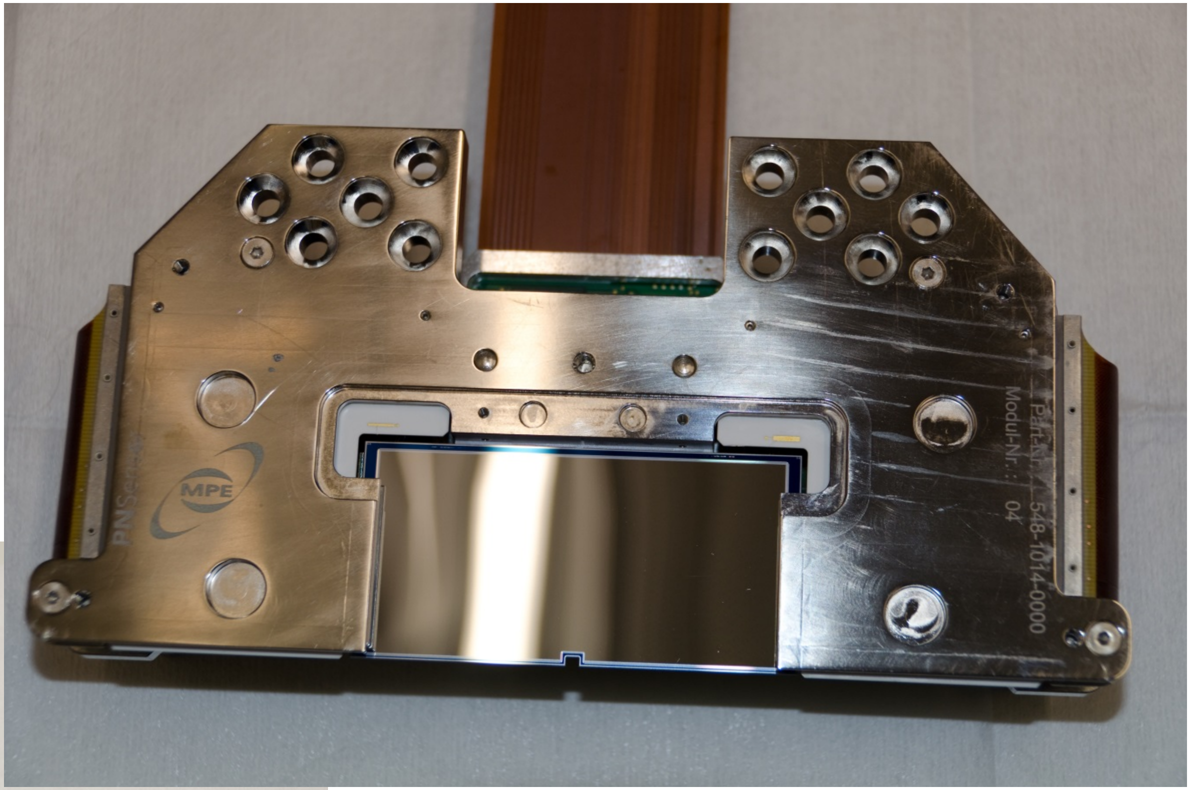
Detectors for LCLS

- **Full sensitive area of system 59 cm²**
- **1024x 1024 pixels of 75 x 75 μm²**
- **Readout time per frame 4 ms - 250 frames / s**

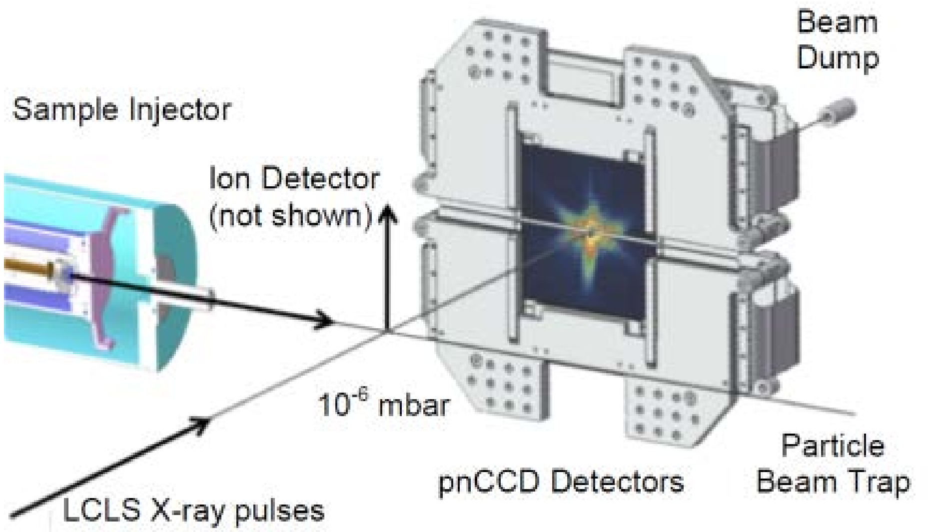


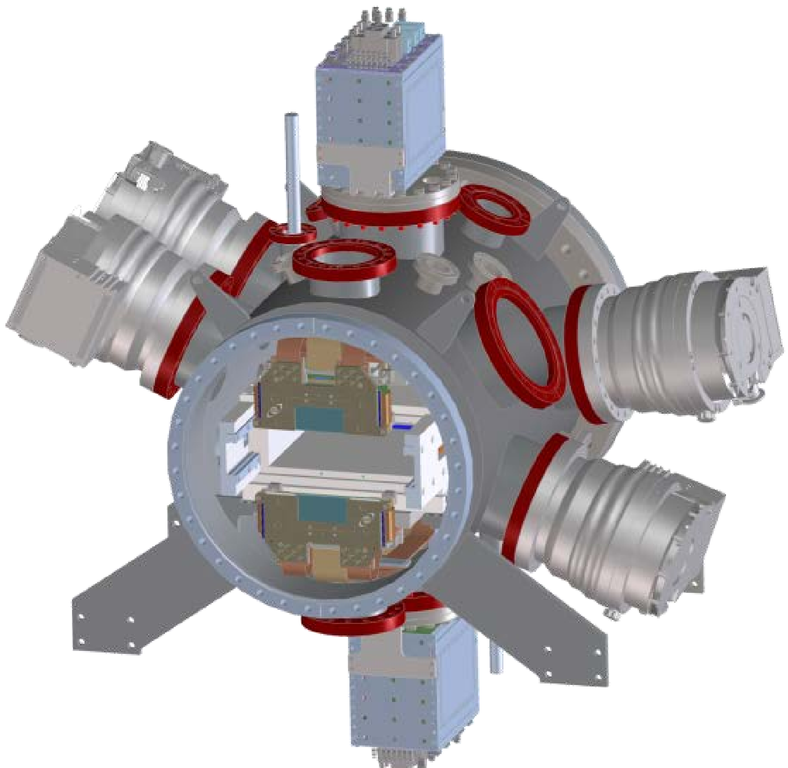
LAMP module

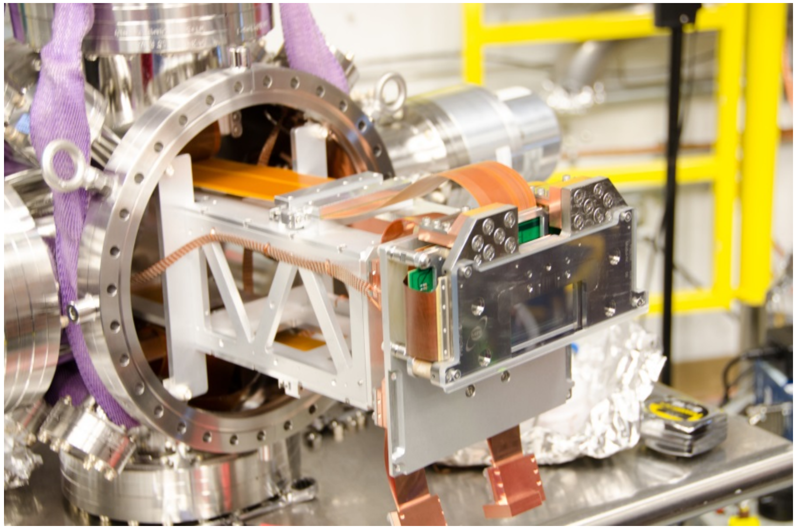




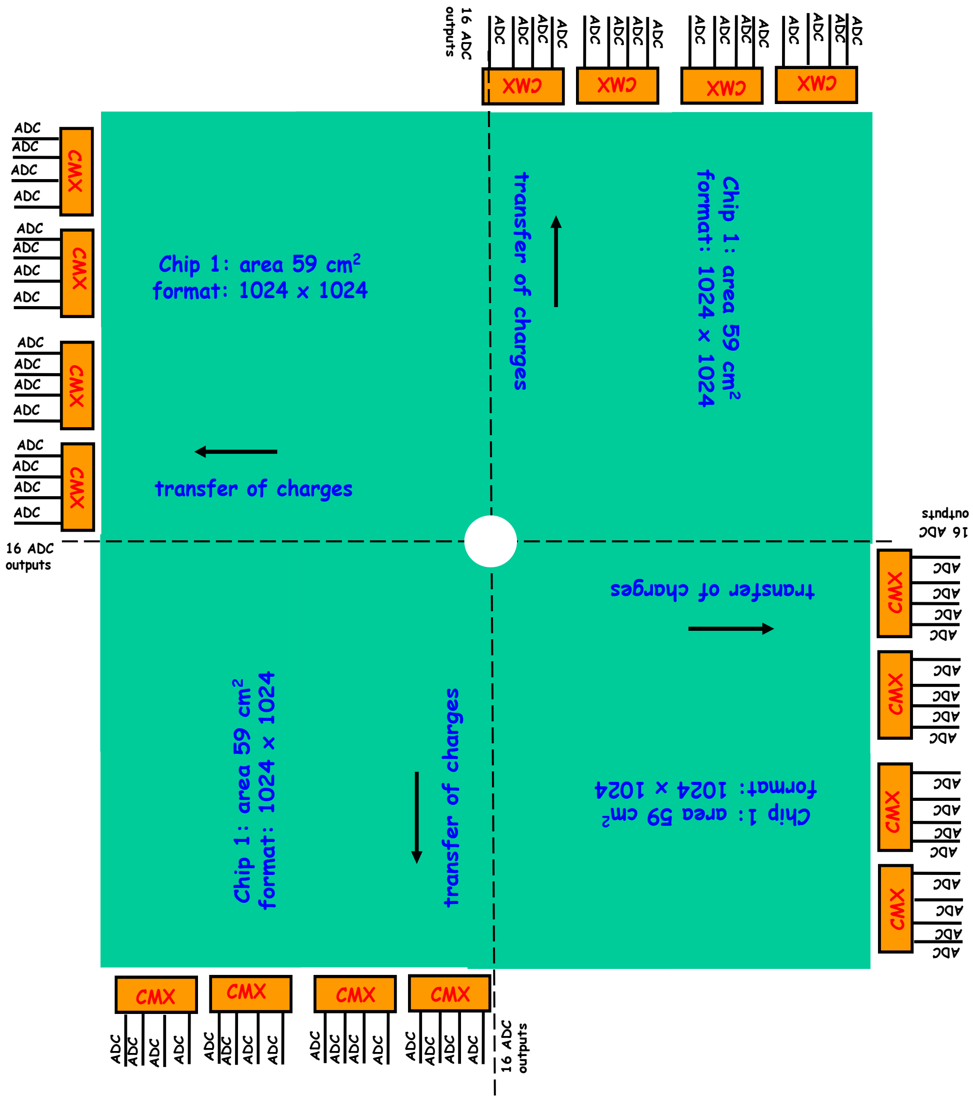
Lamp system @LCLS







Even larger area – two side buttable pnCCDs



- 2048 x 2048 pnCCD array
- pixel size: 75 x 75 μm^2
- total area: 236 cm^2
- readout time: < 8 ms
- read noise < 15 electrons
- Charge handling capacity: > 1000 photons / pixel
- Energy 0.1<E<24 keV
- thickness: 450 µm
- operation temperature:-10°C

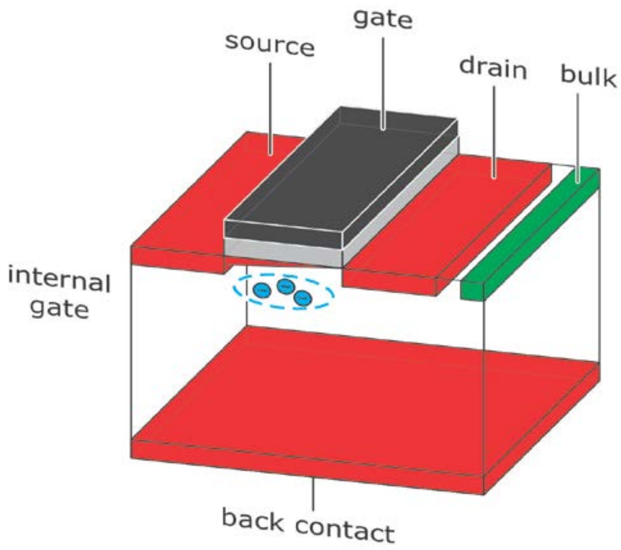
DEPFETs

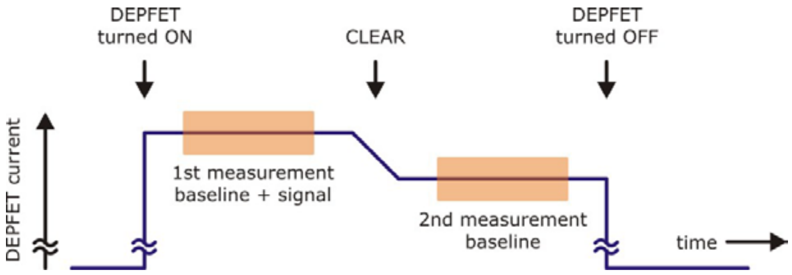
p-MOSFET on fully depleted n-substrate

- **fully depleted** sensitive volume
  - fast signal rise time (~ns), small cluster size
  - no stitching, 100% fill factor
- **Charge collection in "off" state**, read out on demand
  - potentially low power device
  - Non destructive readout
- **internal amplification**
  - charge-to-current conversion (300 pA/el.)
  - large signal, even for thin devices
  - r/o cap. independent of sensor thickness (20 fF)

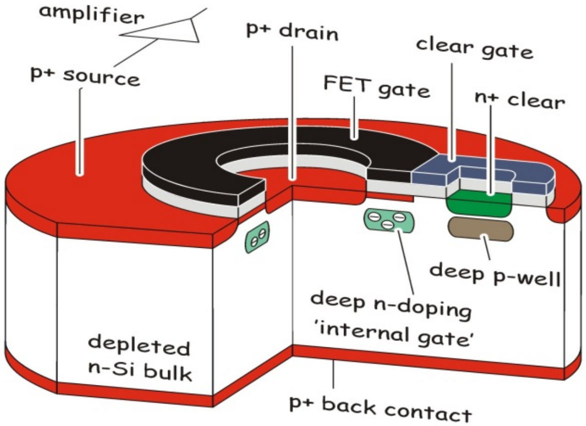
Applications:
- unit cell of active pixel sensor
- integrated readout device of SDD, pnCCD, …

Proposed by
Josef Kemmer &
Gerhard Lutz, 1987



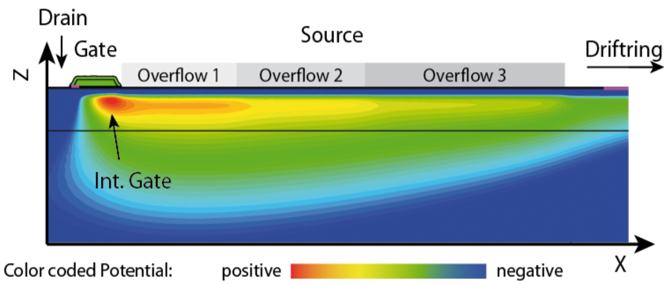


DEPFET classes



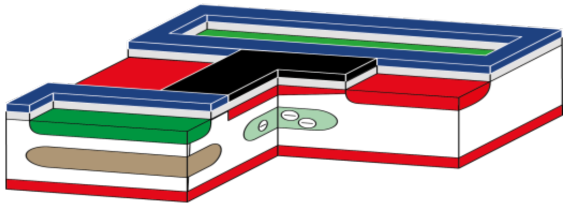
Low noise: Spectroscopic X-Ray imaging

pixel size: 100µm, with drift rings several 100s of µm
read out time per row: few µs
Noise: ≈4 el ENC
fully depleted, the thicker the better → large QE for higher E



High Dynamic range, ultra-fast read-out

DEPFET **S**ensor with **S**ignal **C**ompression
Sensitivity to single photons and high dynamic range
pixel size: ~200 µm
hybrid sensor : 1-to-1 bonded to readout chip



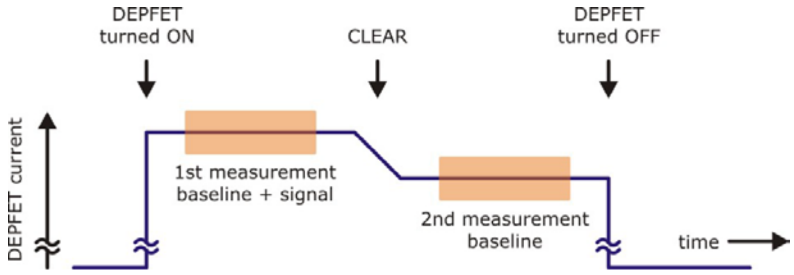
Thin & small pixel: vertex, low E electron detectors (TEM)

pixel size: 20µm…75µm
read out time per row: 25ns-100ns
Noise: ≈100 el ENC
thin detectors: 50µm…75µm → still large signal: 40nA/µm for MIP

DEPFET detectors

DEPFET readout

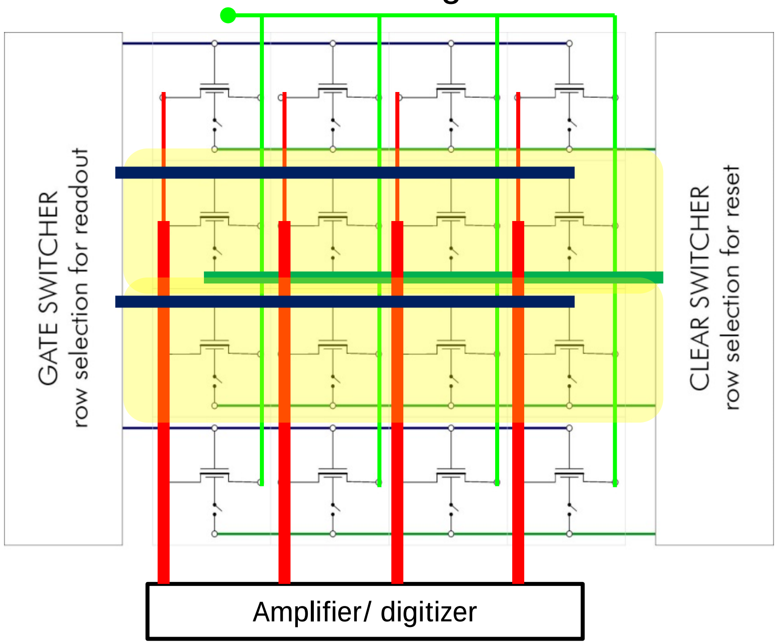
- ▷ readout sequence



- ➢ Double sampling
  - 1st measurement: signal + baseline
  - clear: removal of signal charges
  - 2nd measurement: baseline
  - difference = signal
- ➢ Single sampling
  - Measure pedestals and store
  - Read once and clear

- ▷ active pixel sensor operation
  - horizontal supply lines, row selection
  - vertical signal lines
  - 1 active row, other pixels integrating

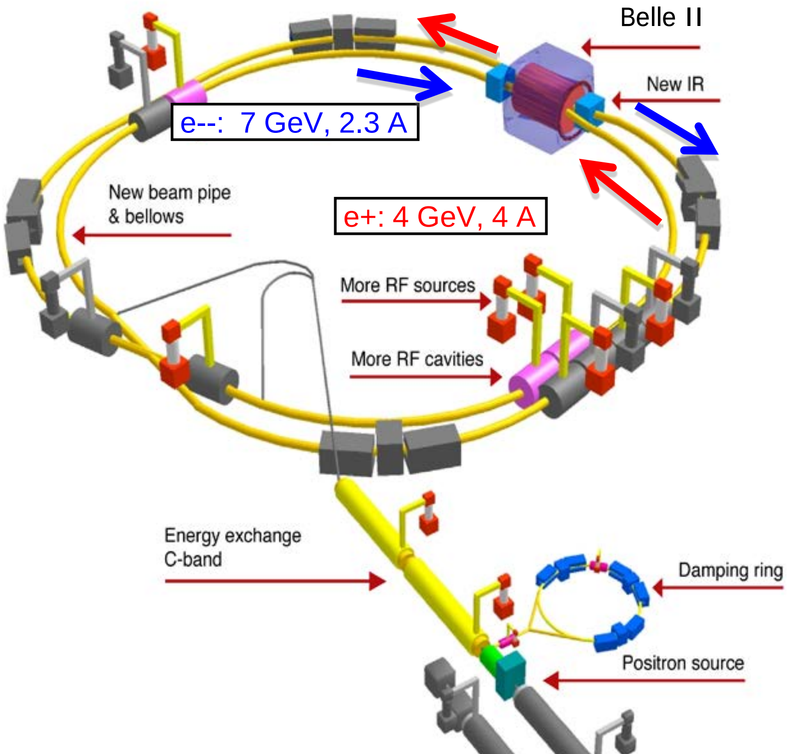
Rolling shutter read out



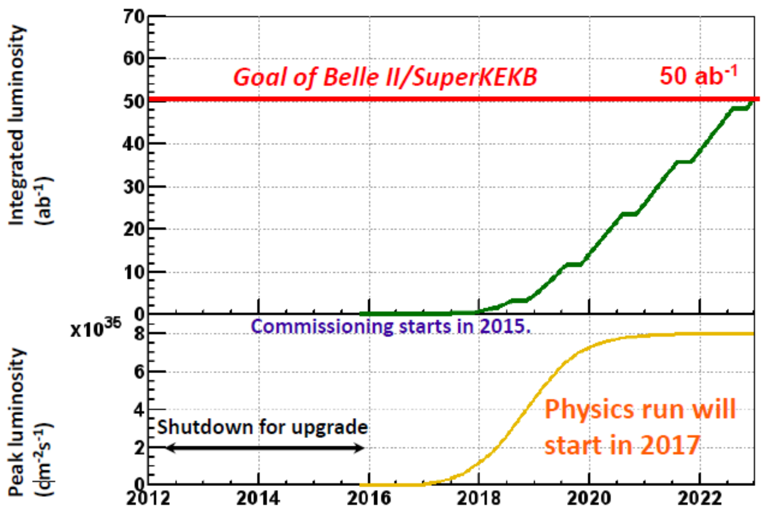
Projects using DEPFETs developed and fabricated @ MPG HLL

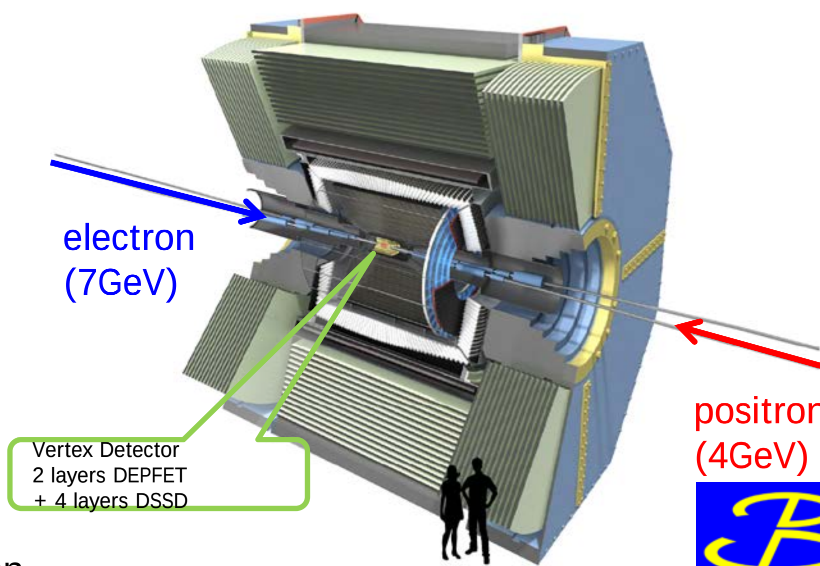
- Vertex detectors for high energy physics experiments
- X-ray fluorescence spectrometer for MIXS on BepiColombo
- X-ray imaging spectroscopy - ATHENA mission – Wide Field Imager (WFI)
- FEL radiation detection – sensors for European XFEL
- Electron Detectors - 80k low E electron detectors

BELLE II @ SuperKEKB

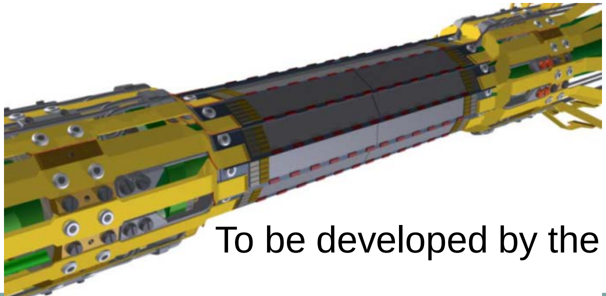


SuperKEKB luminosity projection





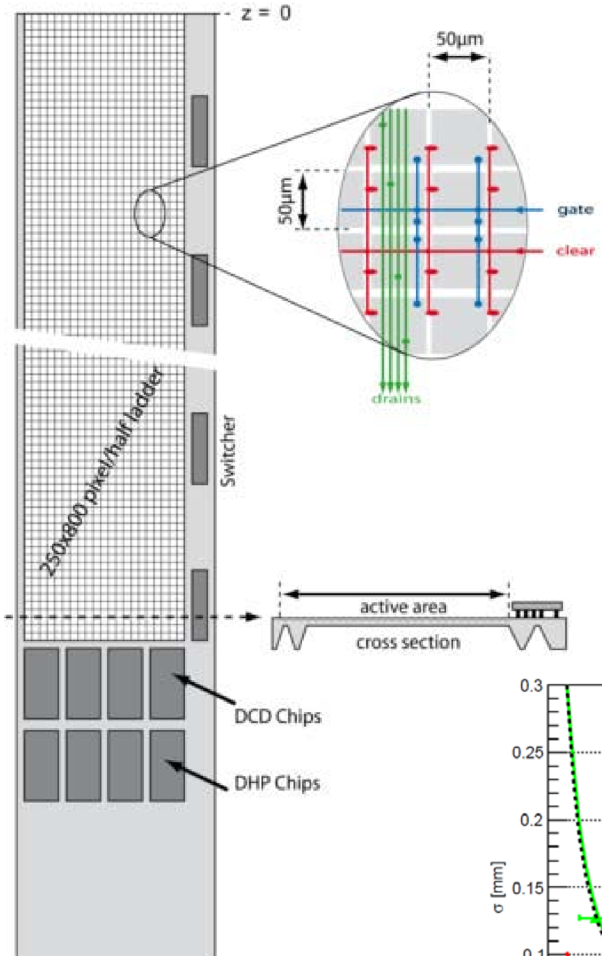
Vertex Detector upgrade
DEPFETs are chosen for the inner layers



To be developed by the DEPFET collaboration

DEPFETs for BELLE II vertexing - Module

All silicon module

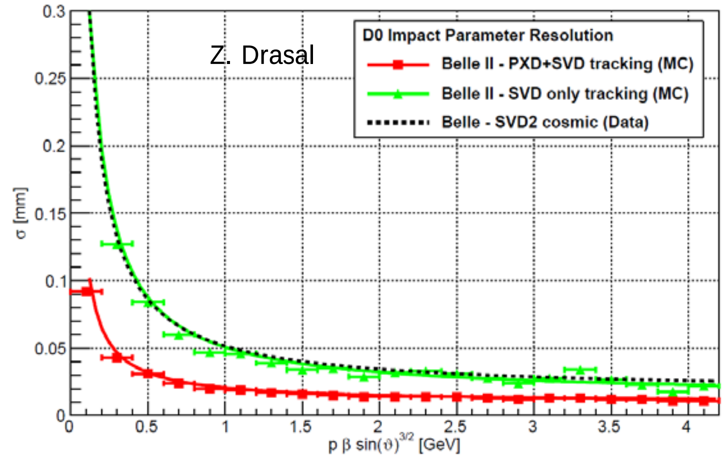


DCDB & SWB developed by UNI Heide
DHP developed by UNI Bonn

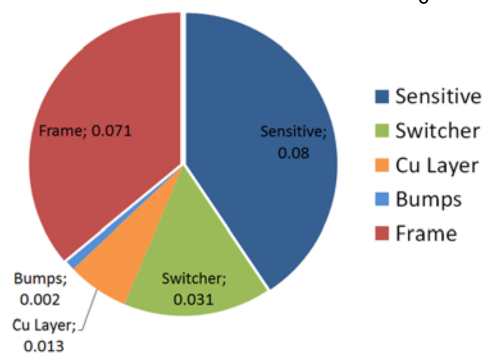
Requirements:

- Single point resolution **~10 µm**
- Radiation **~20 Mrad (10 years)**
- Material budget **0.2 % X_0/layer**
- Frame time **20 µs**

	Inner layer	Outer layer
# ladders	8	12
Sens. length	90mm	123mm
Radius	1.4cm	2.2cm
Pixel size	50x50 µm2	50x75 µm2
# pixels	1600(z)x250(R-ϕ)	
Thickness	**75 µm**	
Frame/row rate	50 kHz/10 MHz	

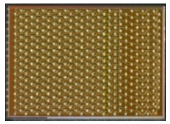


Material contribution 0.2% X_0 measured



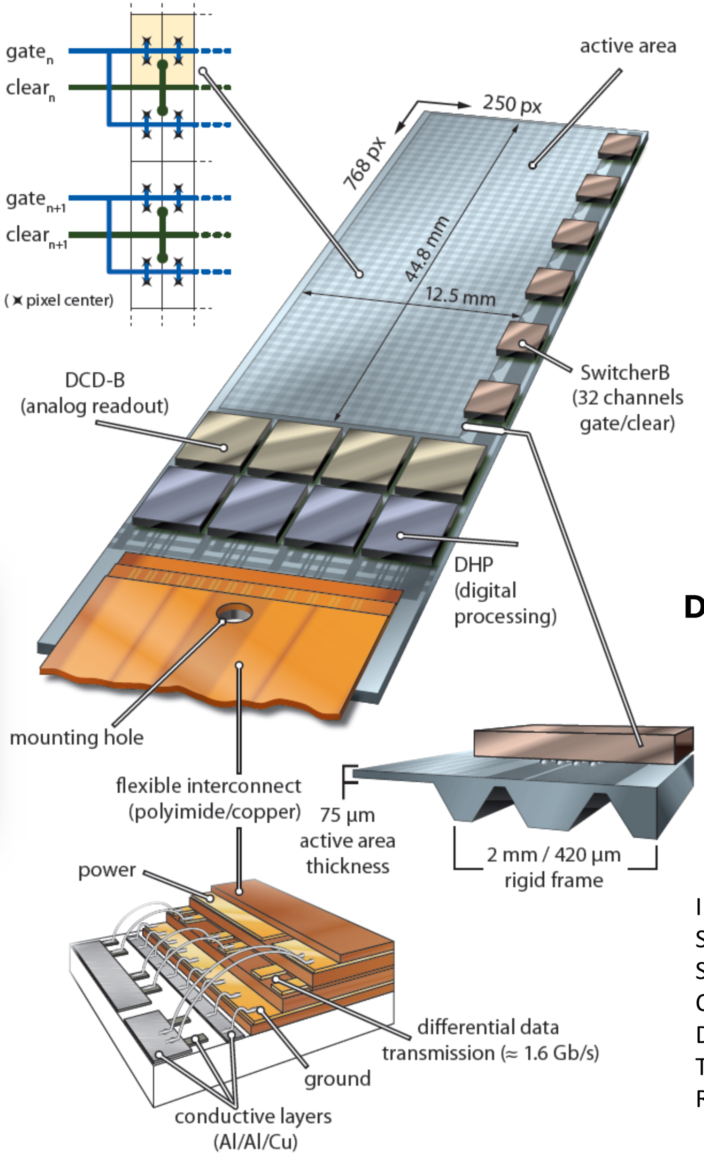
DEPFET all-silicon module

DCDB (Drain Current Digitizer)
Analog front-end

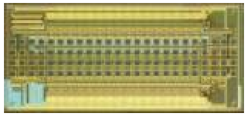


Amplification and digitization of DEPFET signals.

256 input channels
8-bit ADC per channel
92 ns sampling time
UMC 180 nm
Rad hard design



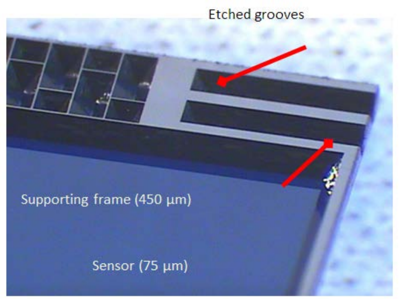
SwitcherB - Row Control



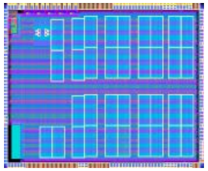
AMS/IBM HVCMOS 180 nm
Size 3.6 × 1.5 mm^2
Gate and Clear signal
32x2 channels
Fast HV ramp for Clear
Rad. Hard proved (36 Mrad)

Low mass vertex detectors

MCMs with highest possible **integration!**
- ↳ Thin sensor area
- ↳ EOS for r/o ASICs
- ↳ Thin (perforated) frame with steering ASICs

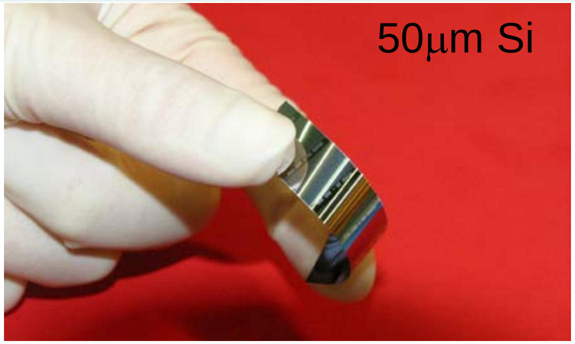


DHP (Data Handling Processor)
First data compression



IBM CMOS 90 nm (TSMC 65 nm)
Size 4.0 × 3.2 mm^2
Stores raw data and pedestals
Common mode and pedestal correction
Data reduction (zero suppression)
Timing and trigger control
Rad. Hard proved (100 Mrad)

Thin DEPFETs for BELLE II PXD



Thin (50µm-75µm) self-supporting all silicon module

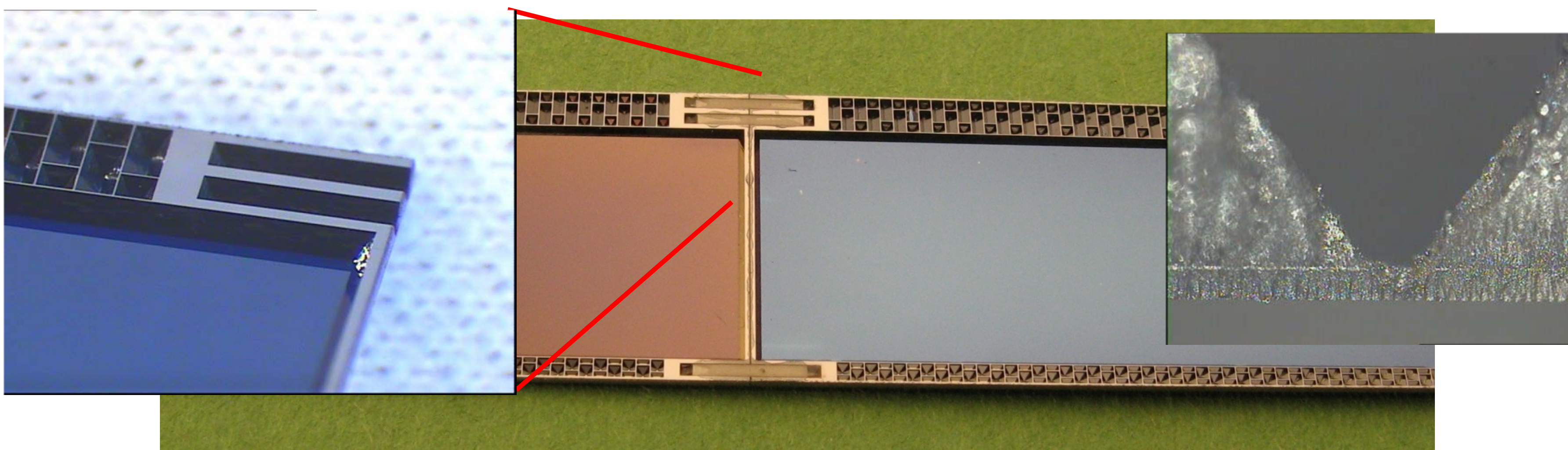
Process backside e.g. structured implant

Wafer bonding SOI process

Thinning of top wafer (CMP)

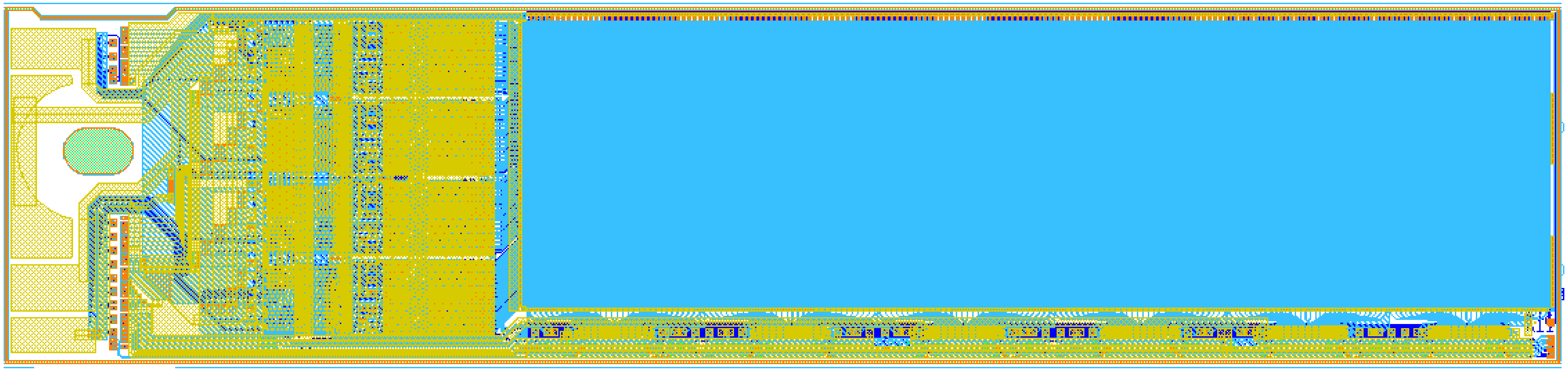
Processing

etching of handle wafer (structured)



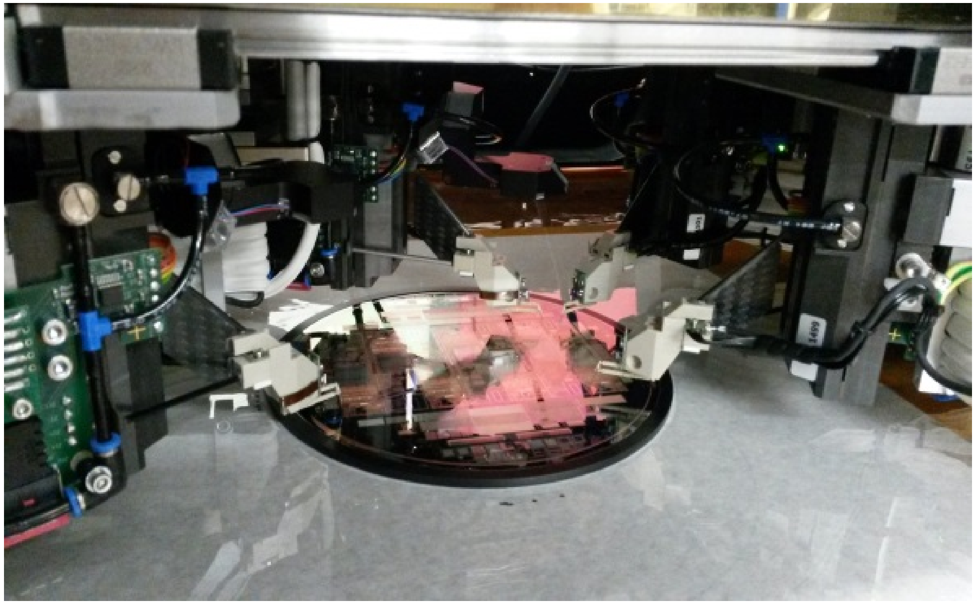
Test vehicle for assembly and electrical performance test

Sensor chips are being produced... in the meanwhile ... Electrical Multi Chip Module optimizations



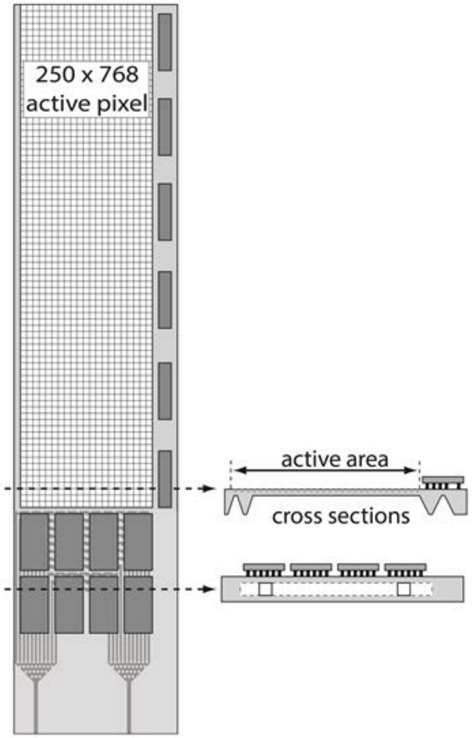
Good die test

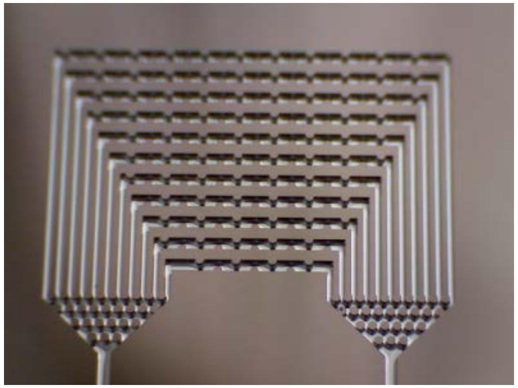
- Sophisticated flying needle testing with O(130k) touchdowns in periphery

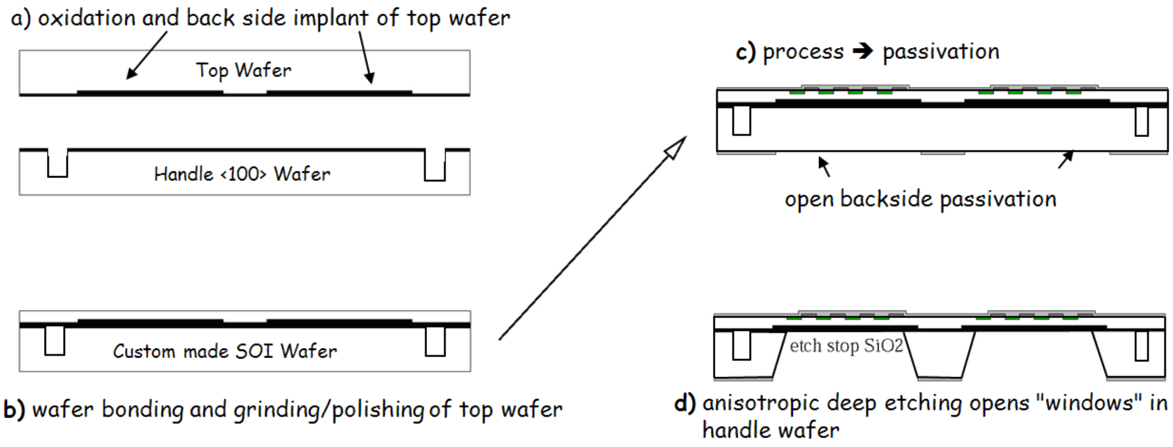


All silicon modules developed for BELLE II vertex detector can be seen as prototype modules for detectors at future Linear colliders

Future all silicon modules - Integrated micro-channels



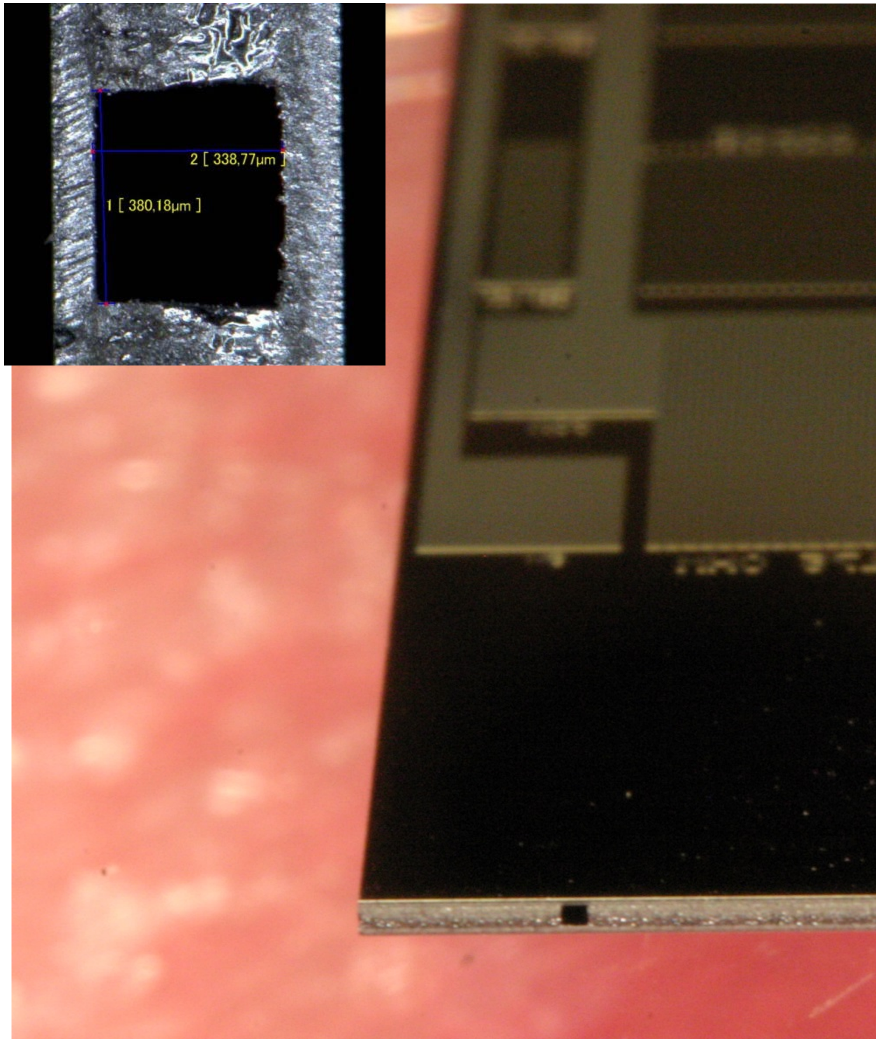


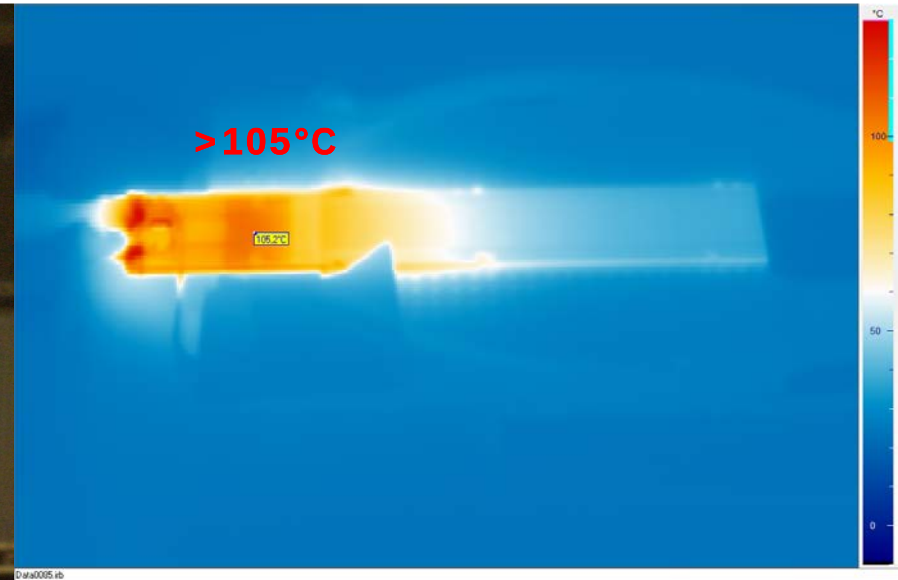


The SOI approach: thinned all-silicon module with integ. cooling

- most heat generated by read-out ASICs
- idea: integrate channels into handle wafer beneath the ASICs
- make use of the thick handle wafer at the end-of-module
- channels etched before wafer bonding → cavity SOI (C-SOI)
- full processing on C-SOI, thinning of sensitive area
- micro-channels accessible only after cutting (laser)

Future all silicon modules / First prototypes for thermal studies

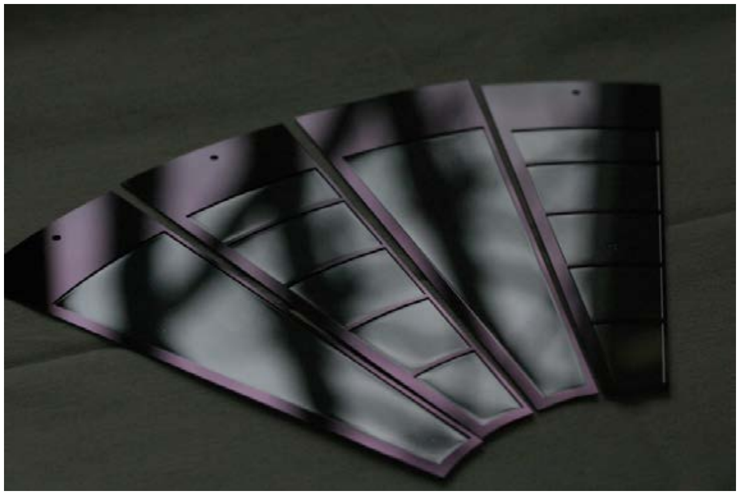


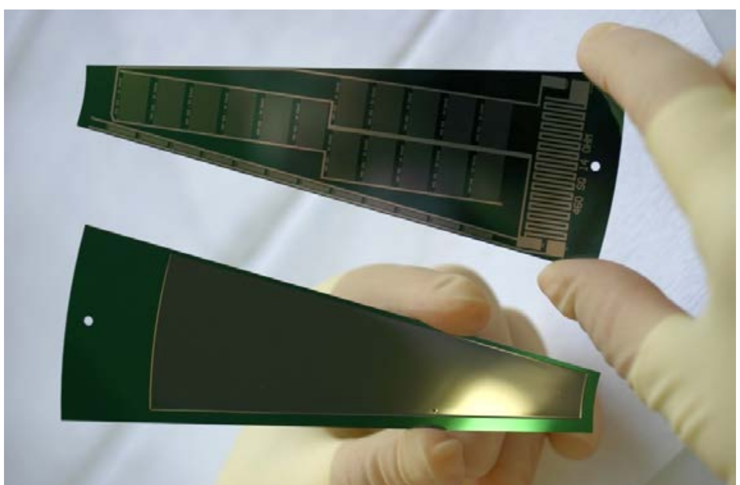


Collaborative work with: University of Bonn and IFIC

Future all silicon modules - Forward tracking disks in ILD

Thermo mechanical Si modules





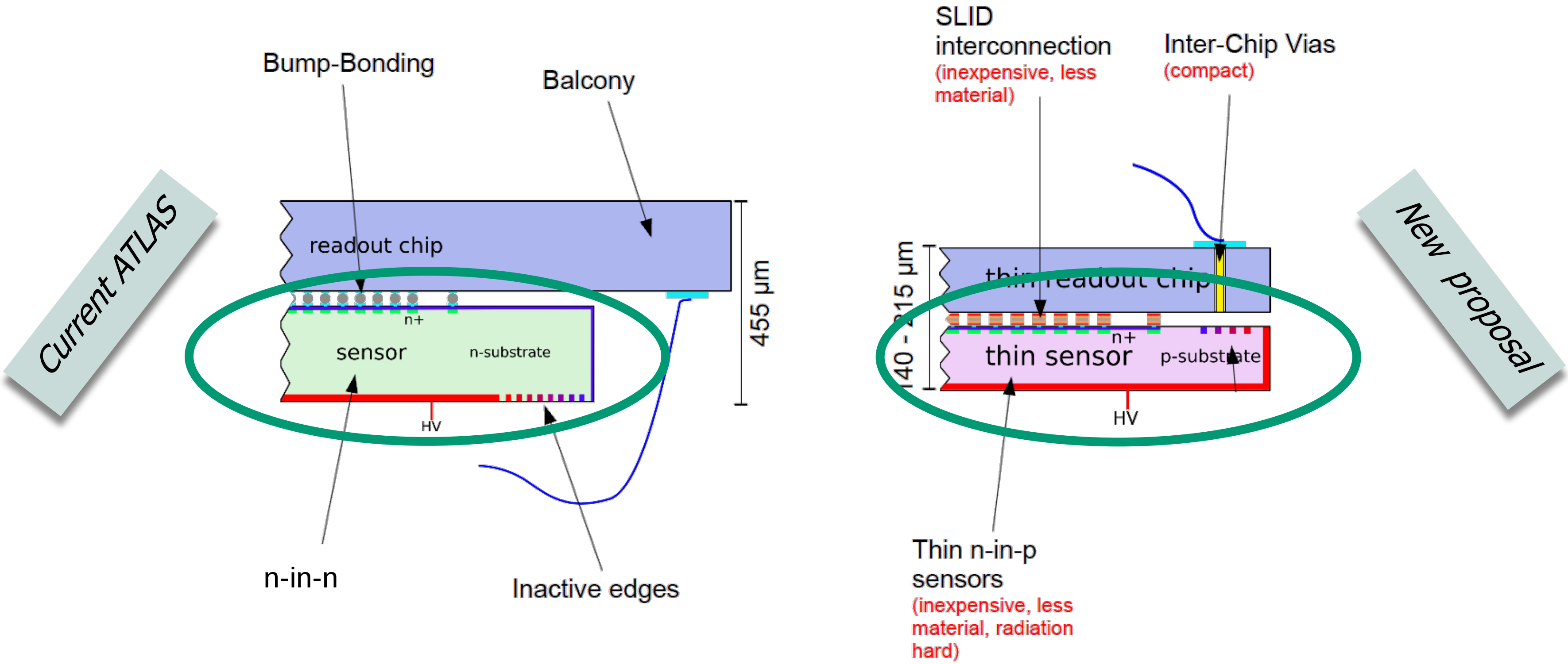
FTD pixel disk mock up

- DEPFET mechanical petals
    - 75 μm Silicon (<0.2% X_0)
- Support disk
    - 1mm (0.09% X_0 avg. area)
- CF connection tubes

Mechanical support structure

Collaborative work with: University of Bonn and IFIC Valencia

The ATLAS Pixel Detector Upgrade – HLL involvement

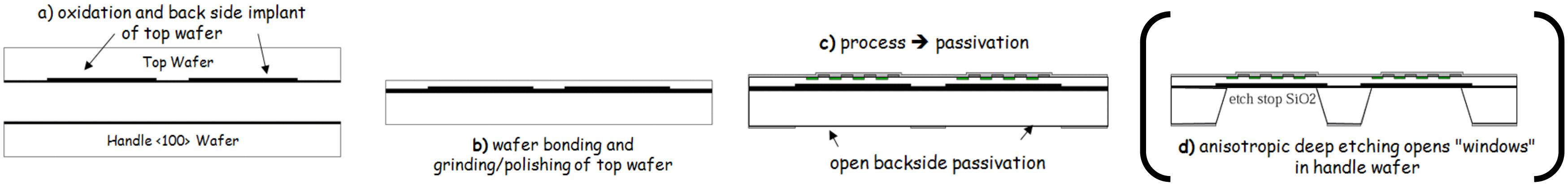


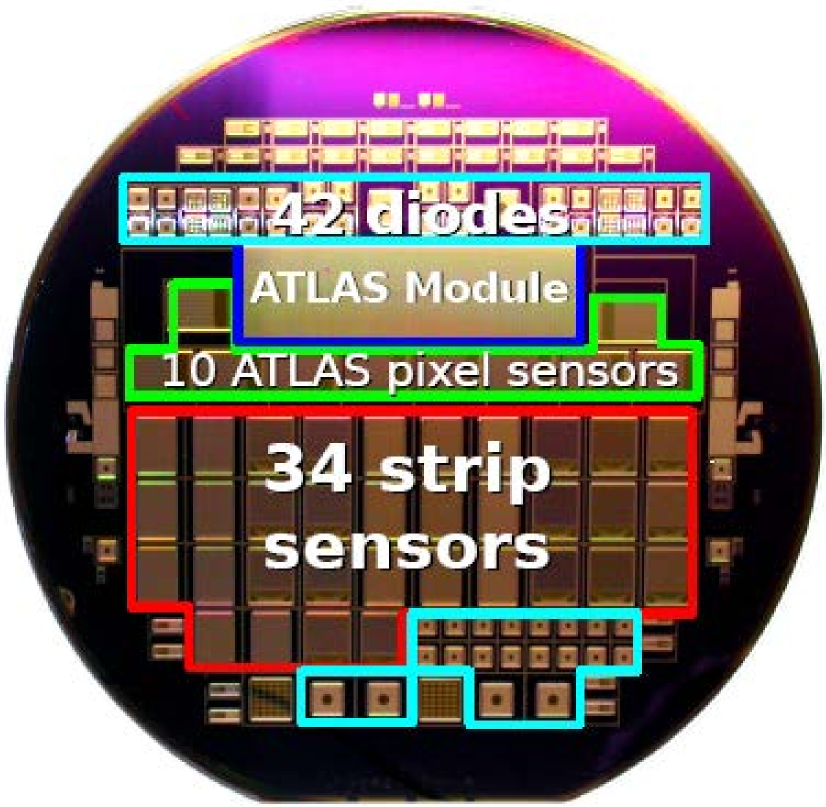
Objectives of the project

- Design and build thin pixel sensors on p-type FZ material
- Show compatibility and radiation hardness of sensors with SLID metal system
- Show feasibility of the post-processing of existing r/o electronics (ICV and thinning)
- Build demonstrator module with thin sensors, using SLID and ICV through the r/o Chip

(collaboration partner MP Physics)

Thin pixel Sensors @ MPG HLL



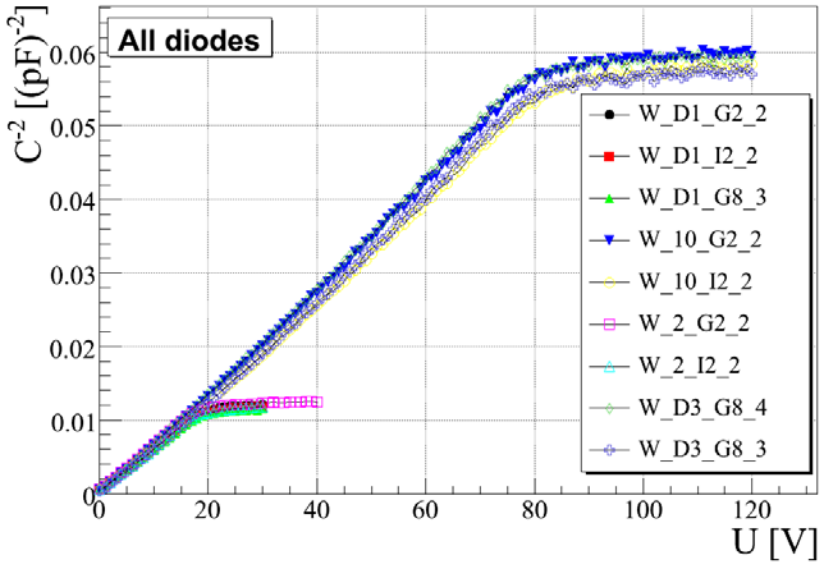


Advantages of thin sensors:

- Lower leakage currents: I ~ V
- Lower full depletion voltage: $V_{fd} \sim t^2$
- Potentially better radiation tolerance
- ... less material

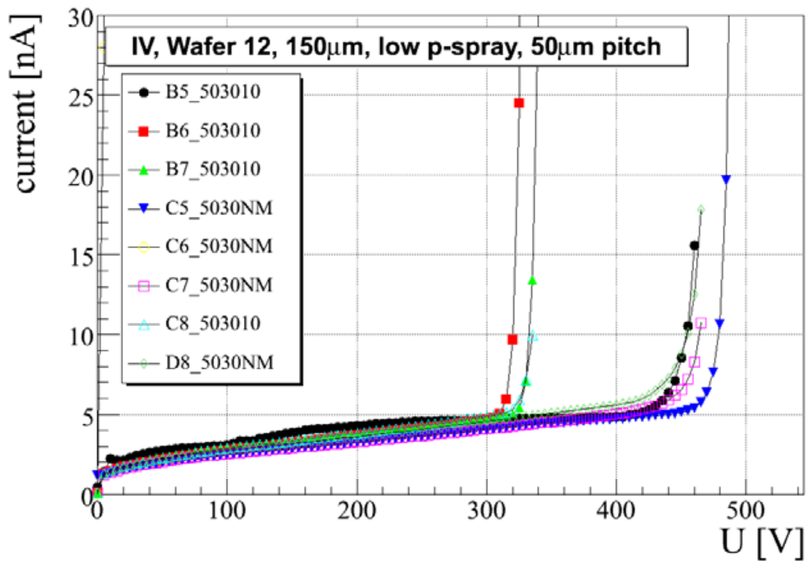
Thin sensor production at MPG HLL:

- n-in-p wafers & n-in-n wafers
- t= 75 µm and 150 µm
- Diodes: technology monitoring
- Pixel sensors: prototype modules
- Strip sensors: charge measurements



Capacitance characteristics (Diodes)

- 150 µm thin sensors: Vfd~80V.
- 75 µm thin sensors: Vfd~20V.
- Scaling $d^2 \sim V_{fd}$ nicely visible.



IV Pixel and mini strip sensors:

- Break down voltage much higher than depletion voltage.
- Low currents before irradiation (<5nA/cm^2).
- also after irrad. (up to 10^{16} n_{eq}/cm^2) very good break down behavior, IV, CCE

X-ray fluorescence spectroscopy: MIXS on BepiColombo

MIXS - First Imaging X-ray spectrometer for planetary X-ray fluorescence

- is the first planetary XRF instrument using a high performance imaging optics, not just a collimator.

Much better spatial resolution!
Look inside craters, identify more features!

- is the first planetary XRF instrument using an energy dispersive solid-state detector

with excellent energy resolution and low energy threshold.
Allows to observe the important lines of Iron, Silicon, Magnesium etc. directly!

DEPFET Macropixel Matrix

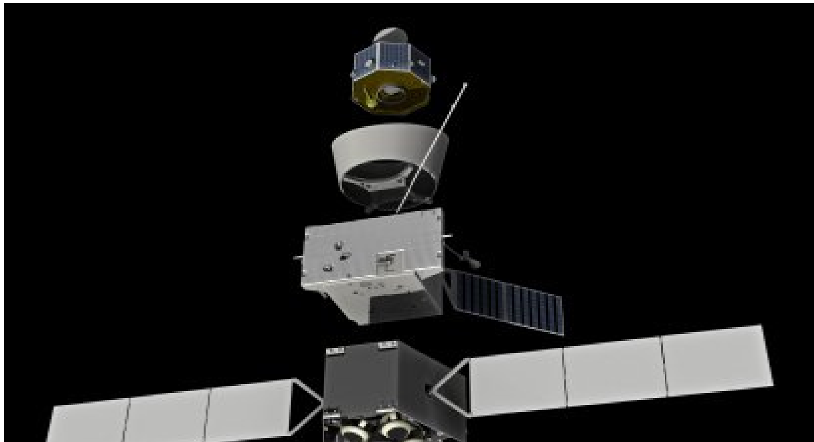
▷ Format
- **1.92 x 1.92** cm^2
- **64 x 64** pixels
- **300 x 300 μm^2** pixel size

▷ Energy resolution
- **200 eV FWHM @ 1 keV**
- QE > of 80 % @ 500 eV

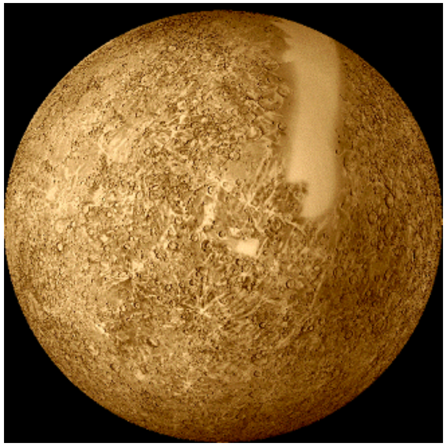
▷ Time resolution
- **< 1 ms** due to dynamics

▷ Radiation hardness
- ~ 20 krad ionizing
- 3×10^{10} 10 MeV p/cm^2
- **equivalent to** 1.11×10^{11} 1 MeV n/cm^2

(collaboration partner MP Solar System Research)

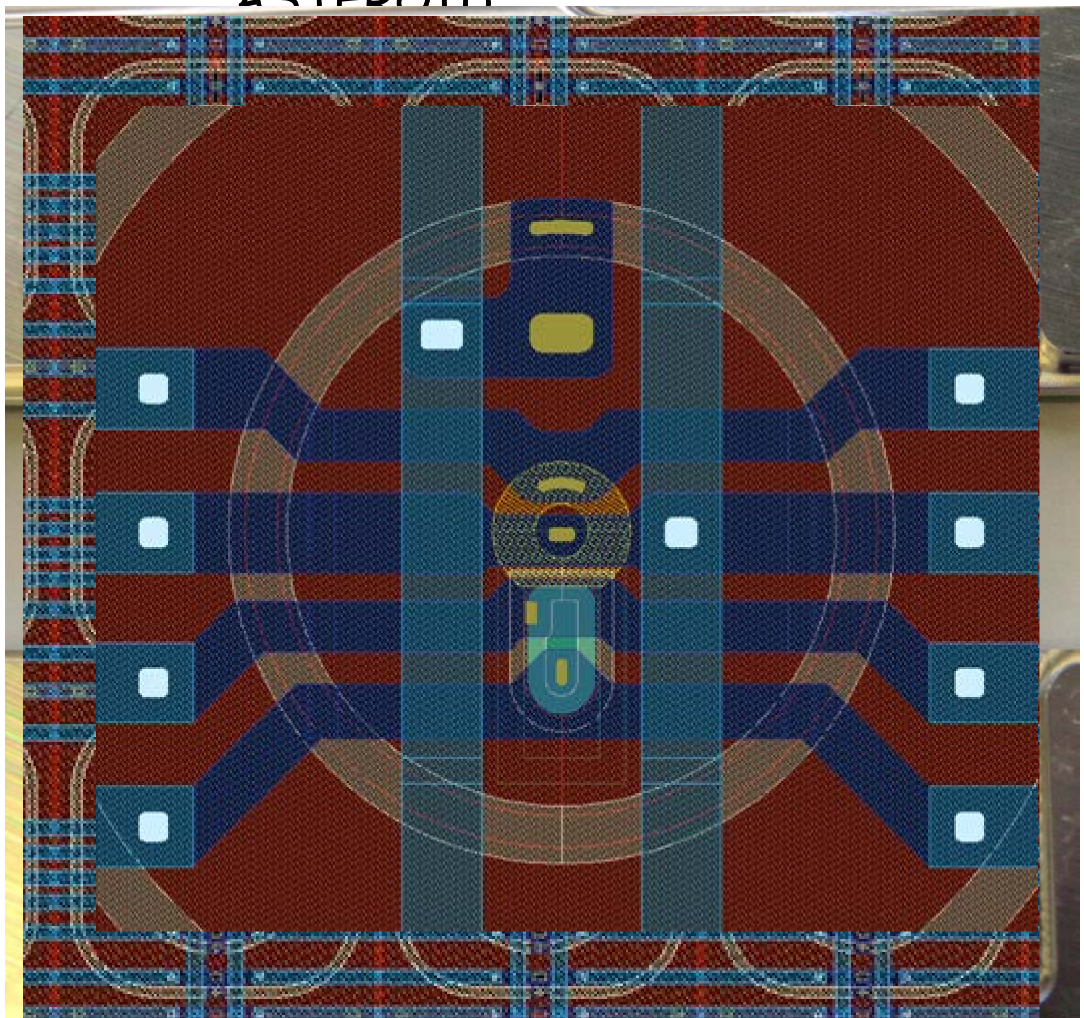


Mercury composite spacecraft (MCS)

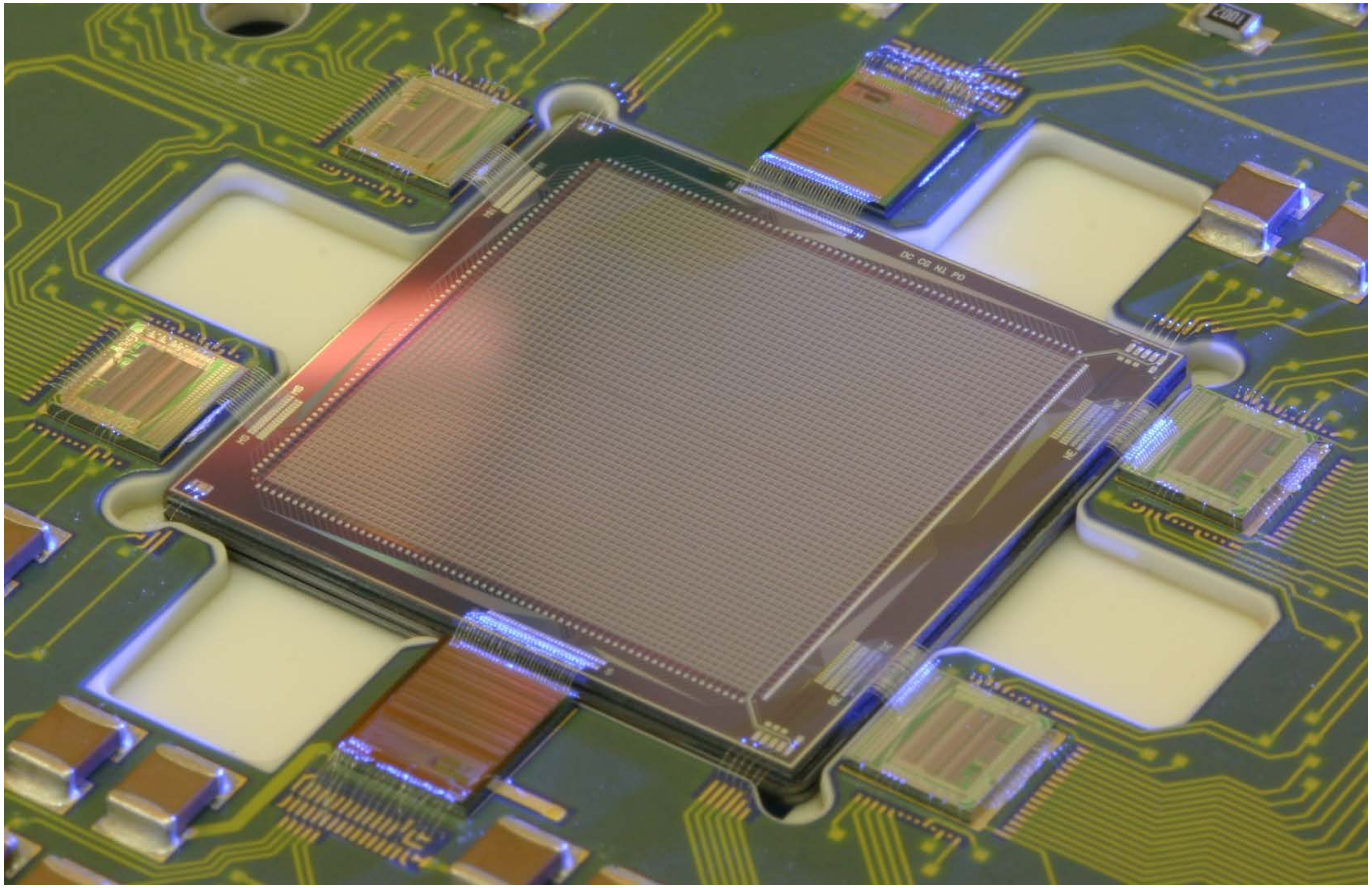


Mercury surface as seem by Mariner 10

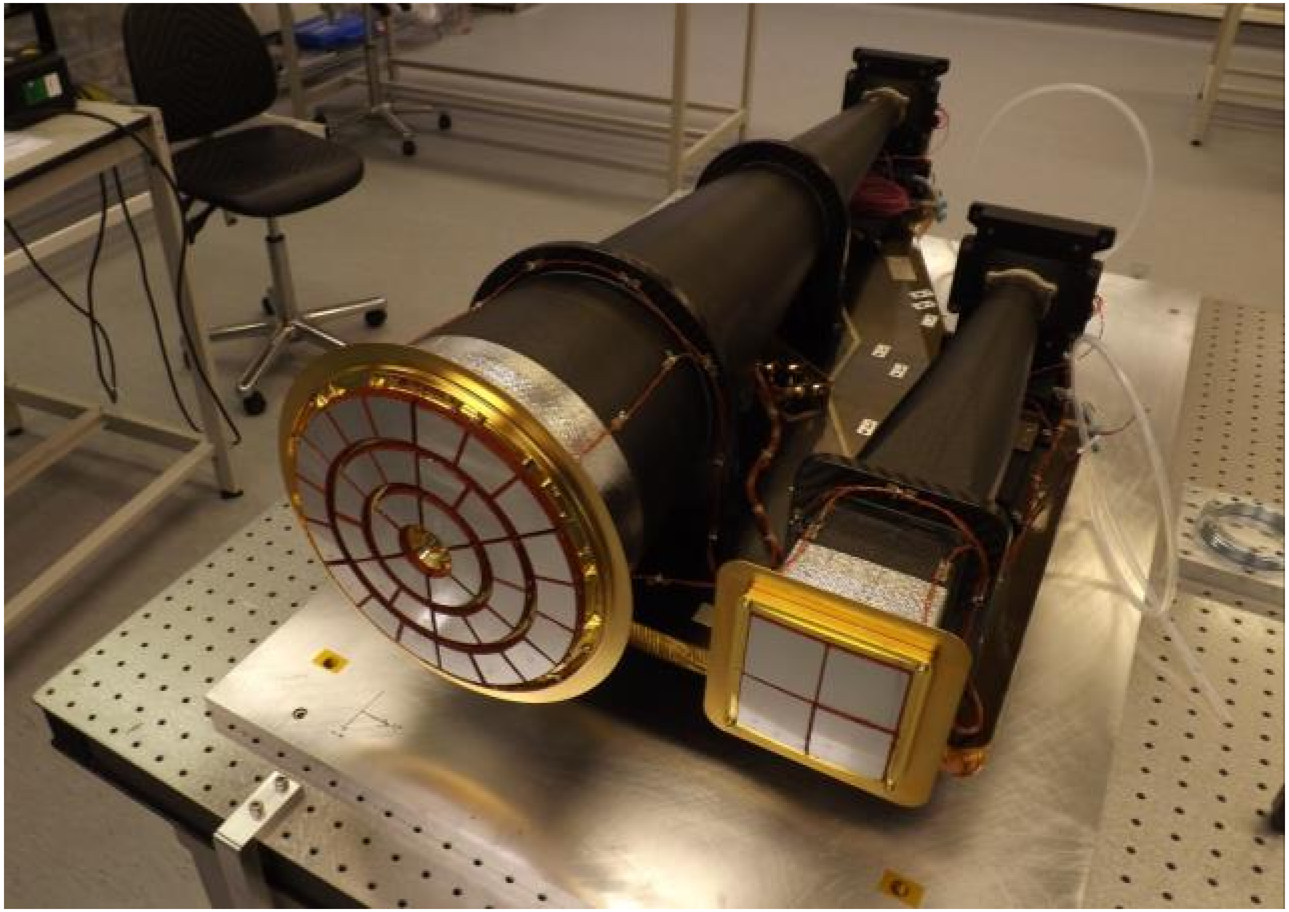
Detector overview



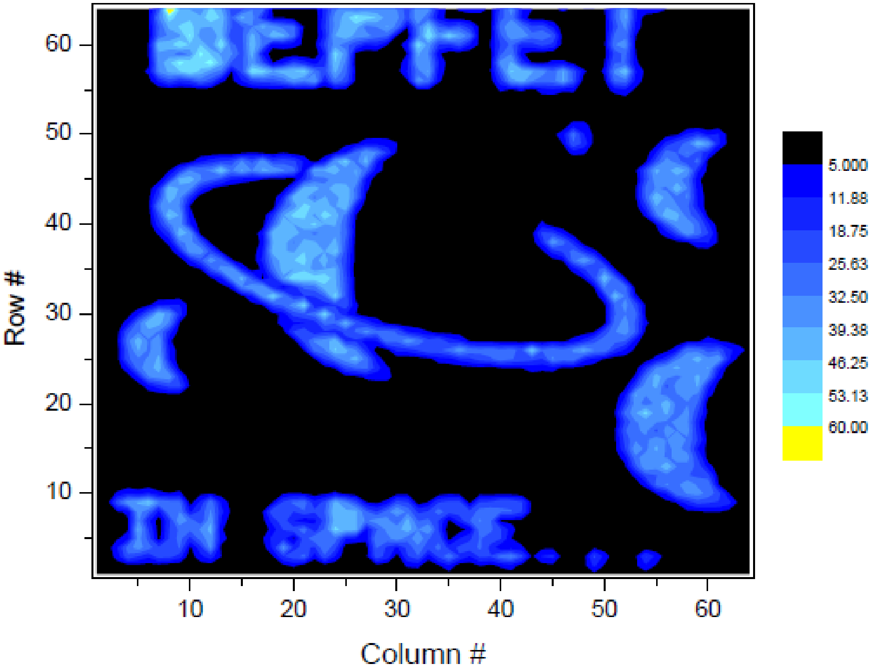
MIXS hybrid



Fully assembled Qualification Model



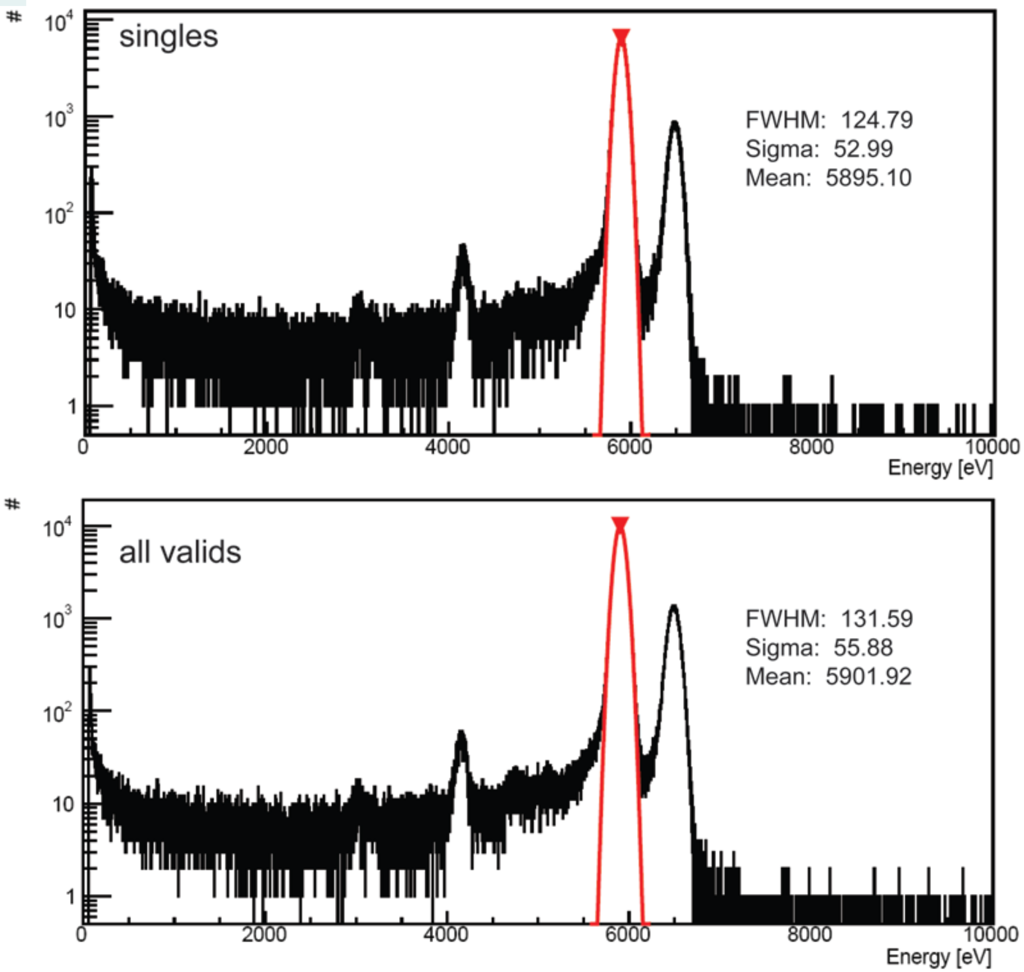
Measurements

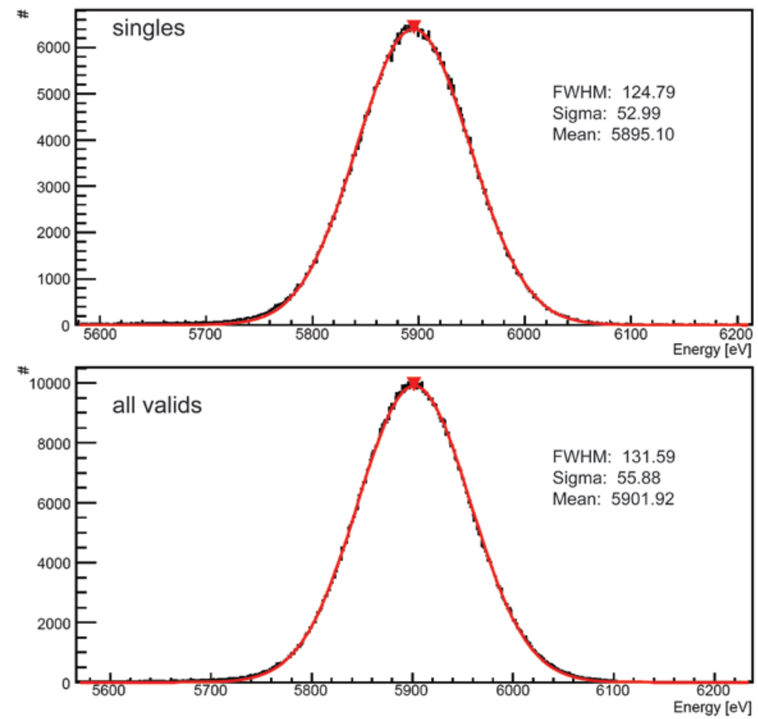


- **Operating conditions**
  - -40 °C
  - T_{row} = 5.2 μs
  - T_{frame} = 167 μs / frame
  - Framerate ~ 6 kfps
  - I_{pixel} = 125 μA

Shadow image of a 450 μm thick silicon baffle with an ^{55}Fe source mounted directly in front of the sensor

Spectral performance



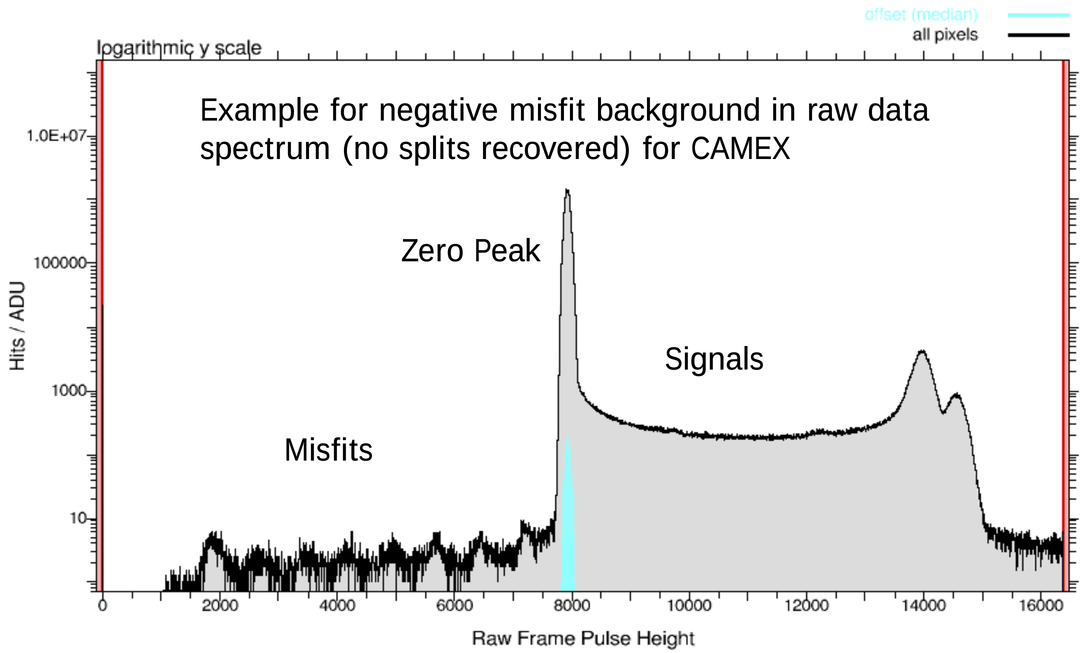


- ^{55}Fe source
- singles: FWHM = 124.8 eV @ 5.9keV
- T ~ -85°C
- 415 µs/frame

Misfits

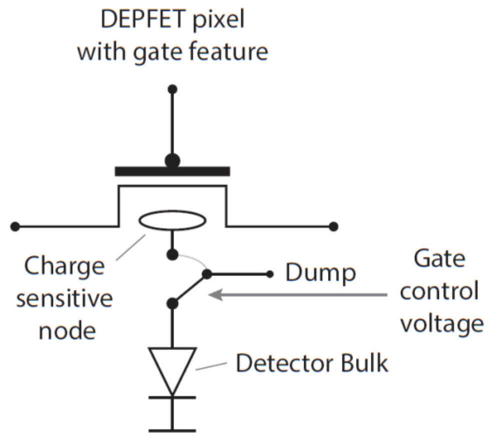
- Events arriving during signal processing time cause “negative” and “positive” background in signal (Misfits)
- Negative signals are easy to be tagged
- Positive signals cause irreducible background
- Spectral shape corresponds to the negative misfit background mirrored at the zero peak

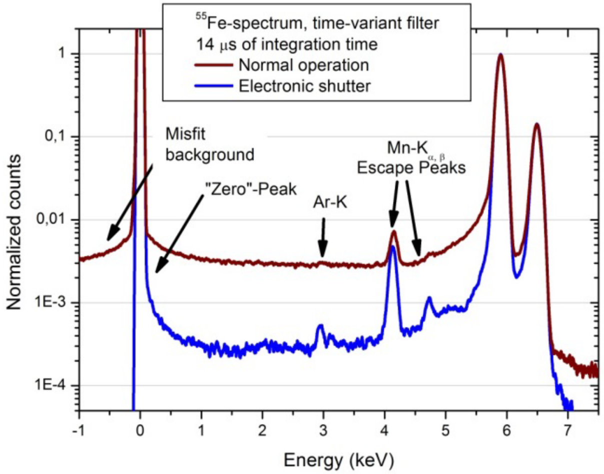
- Fraction of misfits only depends on ratio between readout time and integration time
- Worse for higher degree of parallelization
- Worst case is fully parallel readout (hybrid pixel sensor)
- How to avoid?



Solutions for Misfits

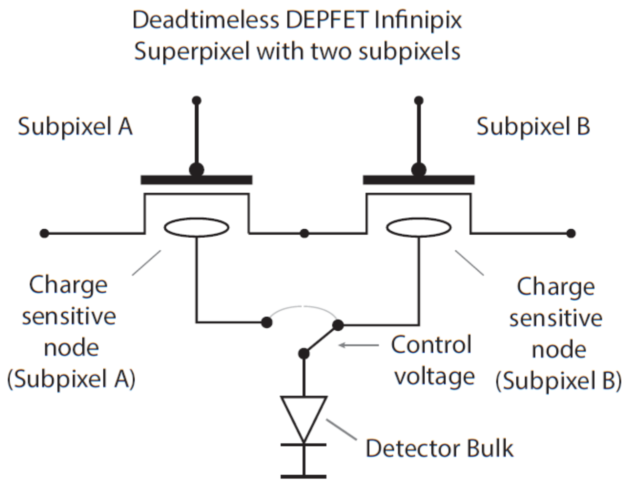
Gated PIX (GPIX)





- Very effective!
- **Drawback: Deadtime!**

InfiniPIX



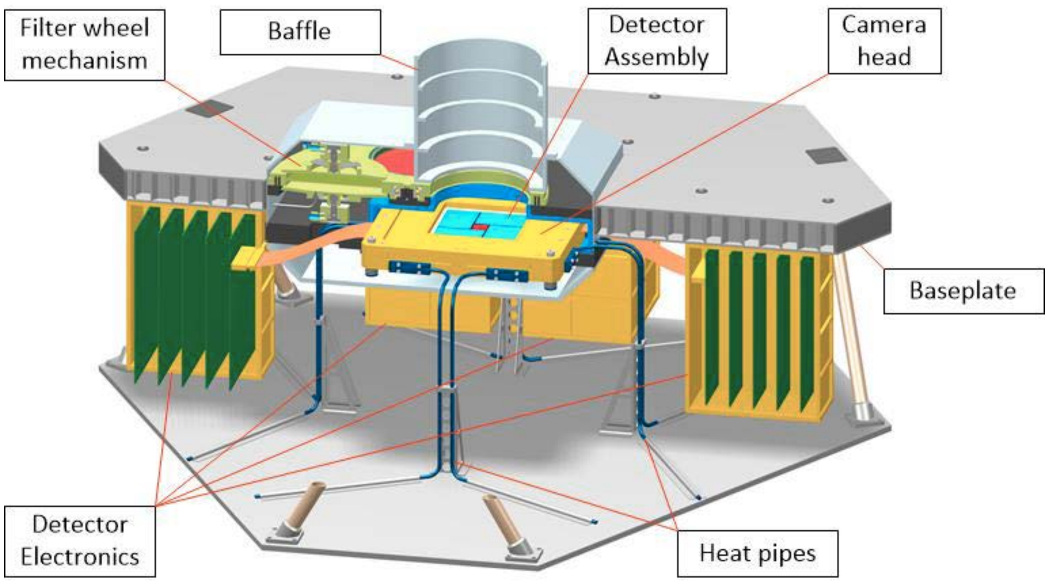
- Superpixel composed of two subpixels
- One subpixel is sensitive. i.e. collects charge from bulk
- The second one is insensitive, i.e. keeps charge already collected, but no new charge will be added, as it is collected by sensitive subpixel
- Only insensitive pixel can be read out
- Shielding is achieved by deviating potentials
- Most simple solution: switching the drain potentials of subpixels

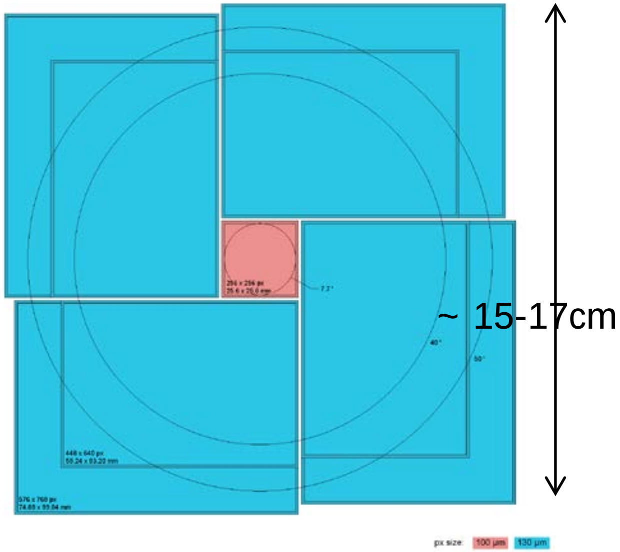
ATHENA mission – Wide Field Imager (WFI)

Athena (the Advanced Telescope for High-Energy Astrophysics), has been proposed as ESA's next-generation X-ray astronomy observatory (Launch slot 2028).
To address two key questions in modern astrophysics:

- How does ordinary matter form the large-scale structures that we see today?
- How do black holes grow and shape the Universe?

(collaboration partner MP Extraterrestrial Physics)

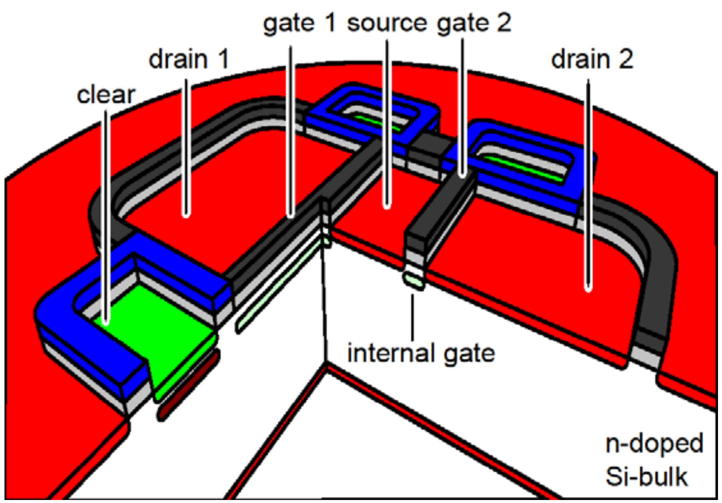


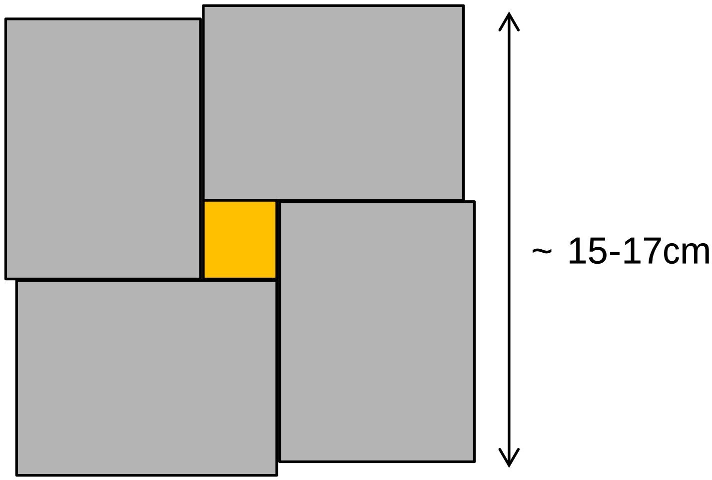


ATHENA mission – Wide Field Imager (WFI)

Central chip: fast timing and high count rate capability

Idea: use infinipix like DEPFET matrix





First prototypes Infinipix DEPFET

->shutter speed < 200ns
->charge suppression < $5*10^{-4}$
->charge handling ≈23500e (≈85keV)

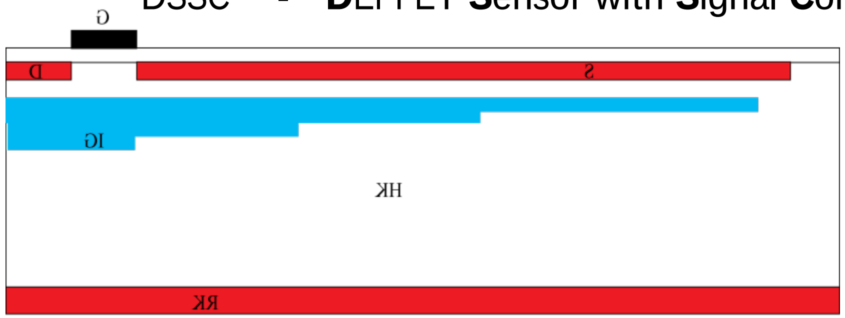
Requirements for the XFEL detectors

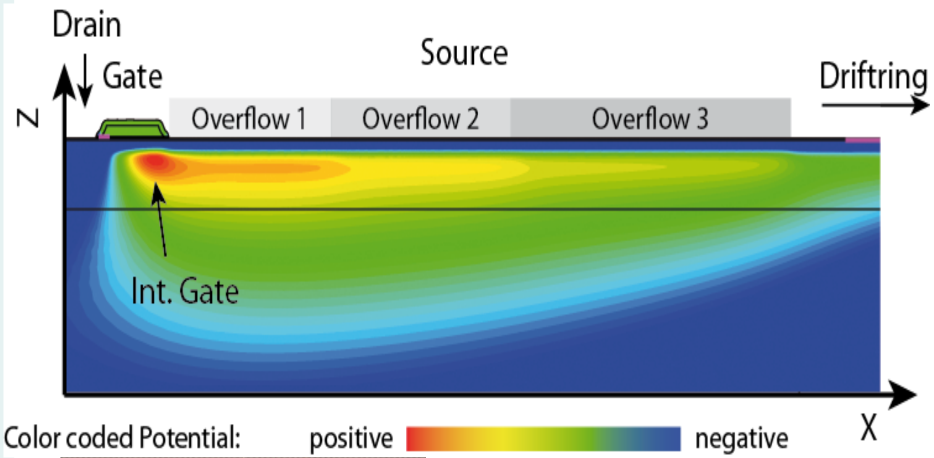
Integrating Area Detector

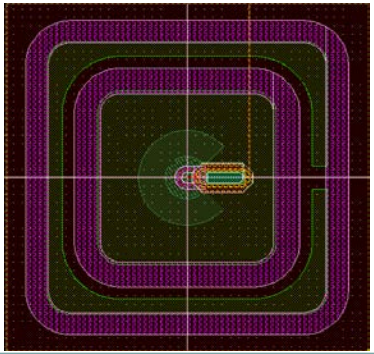
	XFEL (e.g. XPCS)	DEPFET array system
single photon resolution	yes	yes
energy range	0.5< E < 24 (keV)	0.5 < E < 25 [keV]
ang. resolution or pixel size	4 µrad	200 µm
sig.rate / pixel / bunch	10^3	10^3@10KeV
quantum efficiency	> 0.8	> 0.8 from 0.3 to 12 keV
number of pixels	512 x 512 (min.)	1024 x 1024
frame rate / repetition rate	10 Hz	yes, triggerable
XFEL burst mode	5 MHz (3.000 bunches)	4.5 MHz
Readout noise	< 150 e^- (rms)	< 50 e^- (rms)
cooling	possible	- 20º C optimum, room temperature possible
vacuum compatibility	yes	yes
preprocessing	no (yes) ?	possible upon request
4-side buttability	yes	yes

Detector Concept – DEPFET with signal compression

DSSC - **D**EPFET **S**ensor with **S**ignal **C**ompression

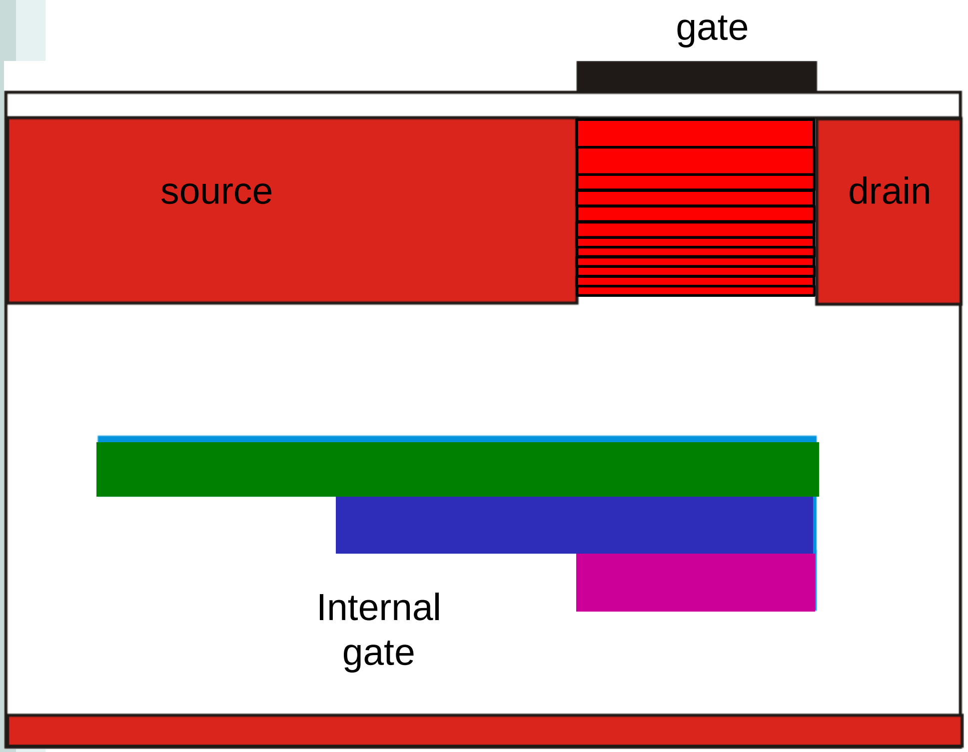


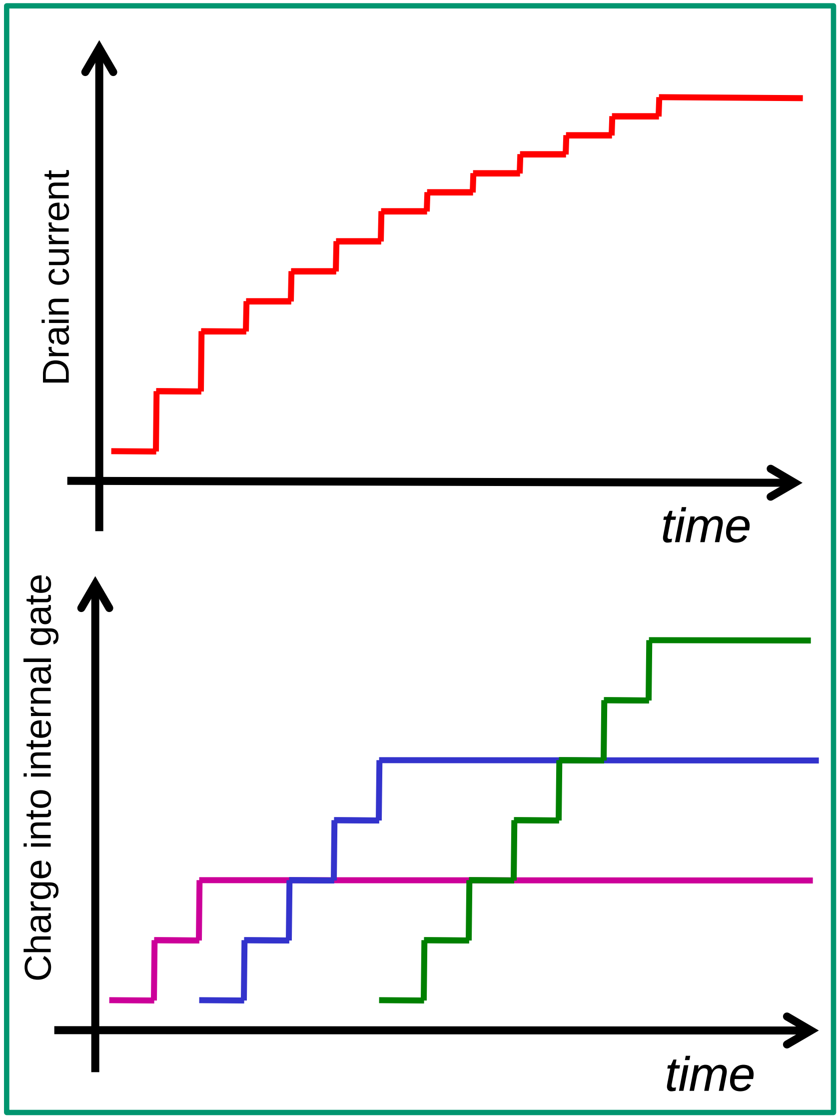




- The internal gate extends into the region below the source
- Small signals assemble below the channel, being fully effective in steering the transistor current
- Large signals spill over into the region below the source. They are less effective in steering the transistor current.
- 200 x 200 μm pixel has been designed and produced

Detector Concept – Working principle

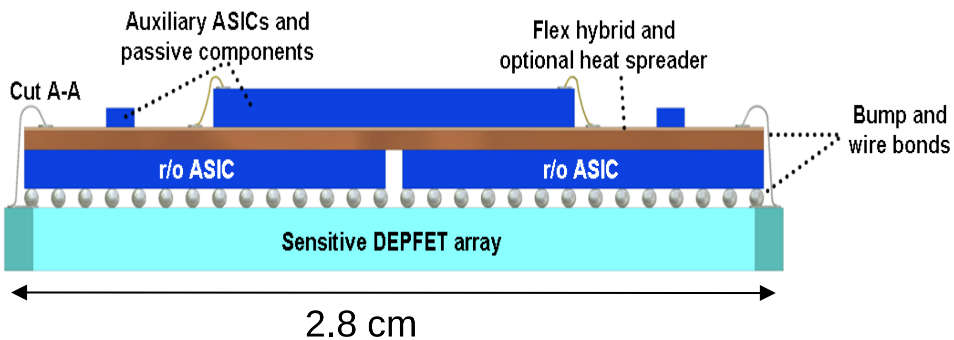


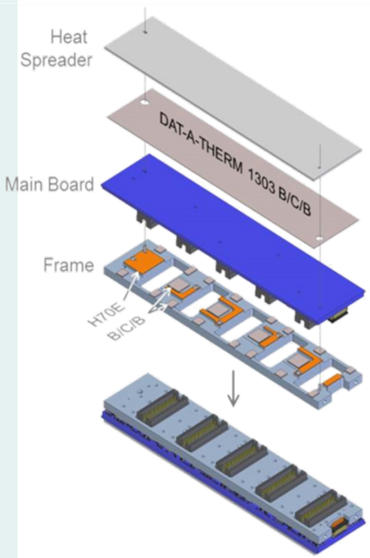


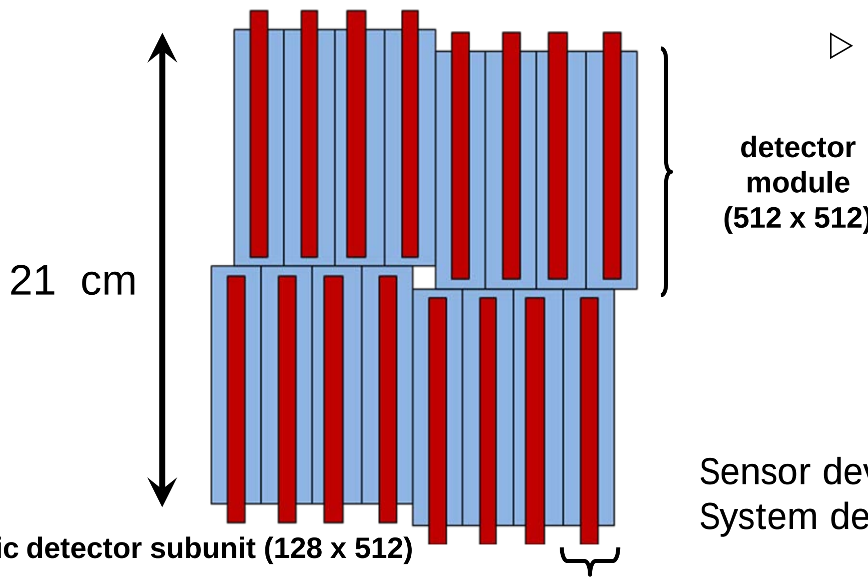
- A constant charge is injected at fixed time intervals and the internal gate regions are progressively filled
- In the experiment the charge is deposited at once but the DEPFET response is the same

Focal Plane

Submodule 128x512







Multi Chip Modules

- DEPFET Sensor bump bonded to Readout ASICs
- Optional Heat spreader
- Flex Hybrid with passive components and auxiliary ASICs (e.g. voltage regulators)
- Sensor (512x128 pixels) $2.56 \times 10.24\ cm^2$
- 16 readout ASICs (64x64)
- Dead area: 10-15%

Sensor development by MPG HLL
System development by DSSC collaboration

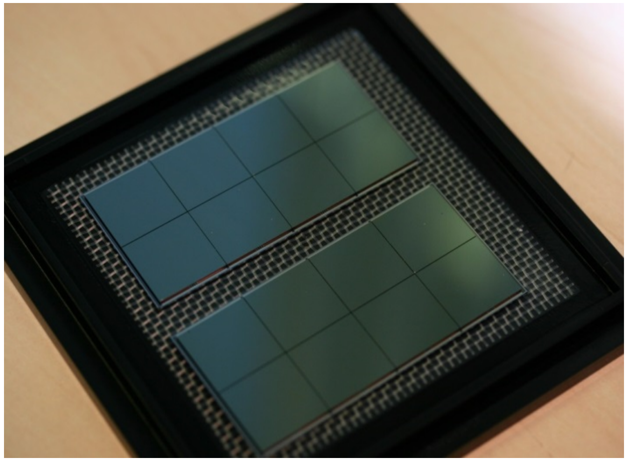
DSSC interconnection and assembly

In House Flip chip

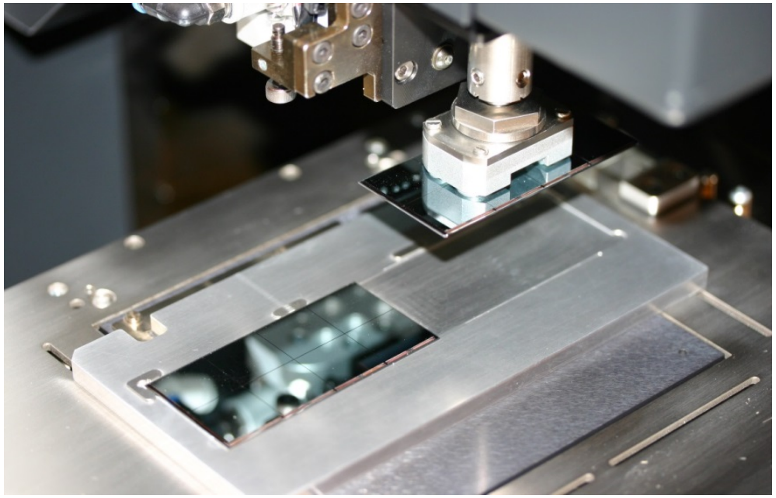
Fully automated flip-chipping

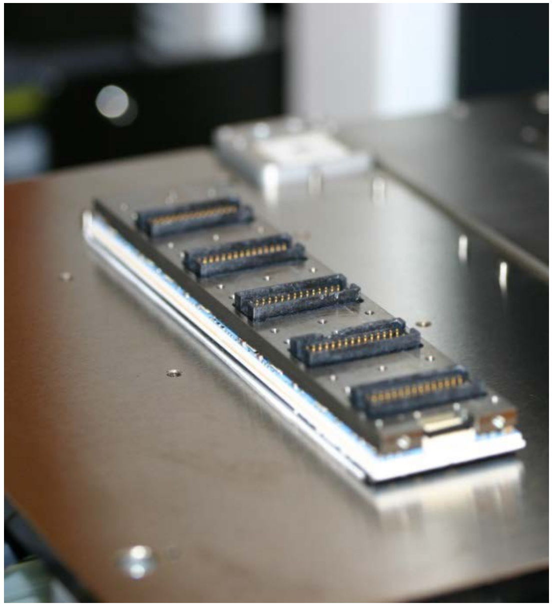
Reproducible yield :

~100% (1-3 missing bonds out of ~33000)



Macro-assembly equipment installed

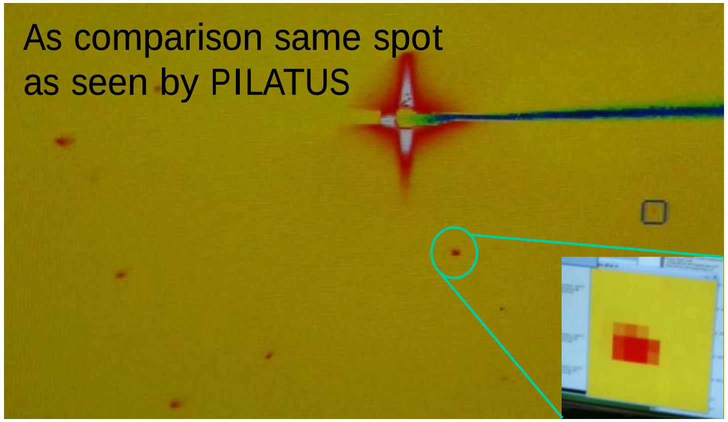


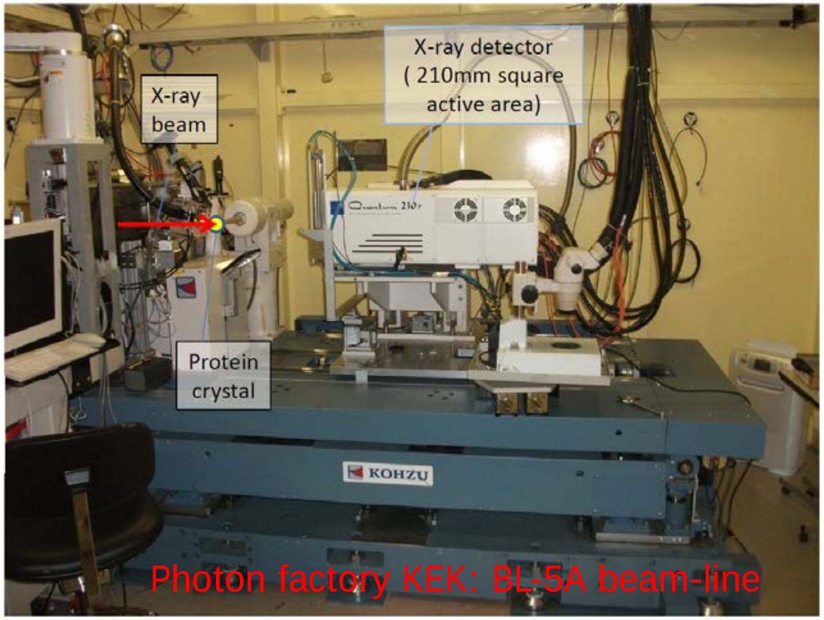


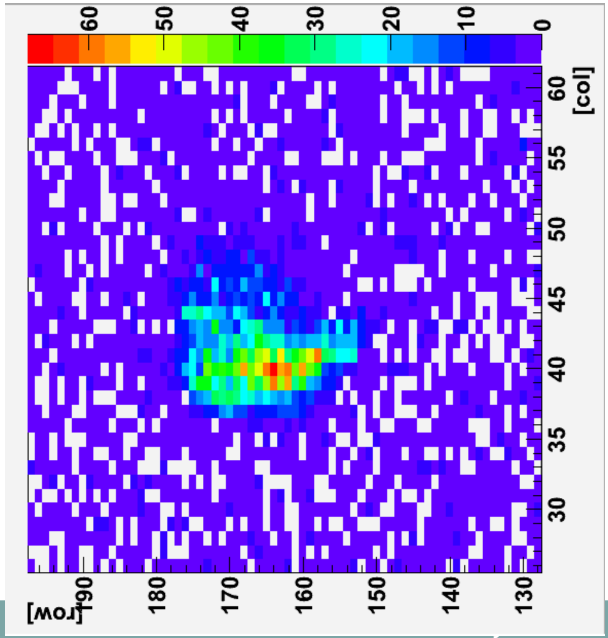
BELLE & ILC DEPFETs for Photon Science

First tests: slow readout system 2.3ms frame readout time (signal integration time) with about 150Hz DAQ readout rate (one frame is read out every 6ms)

Matrix – ILC type 24x32μm² pixel 450μm thick
5120μm x 1280μm (256 x 64 pixels)



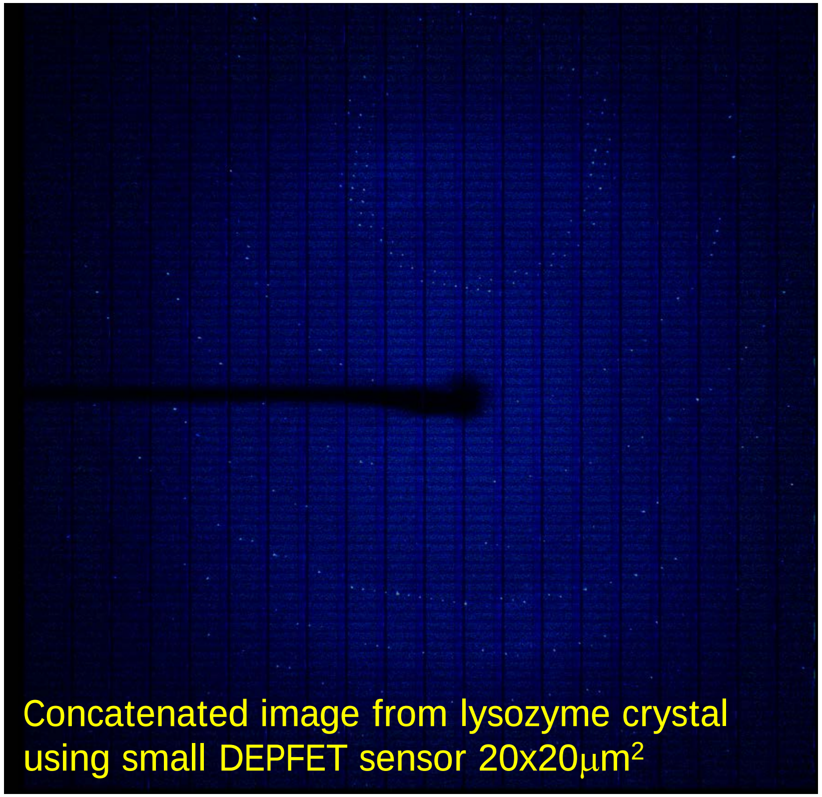




Lysozyme crystal – position of diffraction spots defined by PILATUS and then DEPFET matrix driven to that point

BELLE & ILC DEPFETs for Photon Science

X-ray Diffraction Image from the Protein Crystal

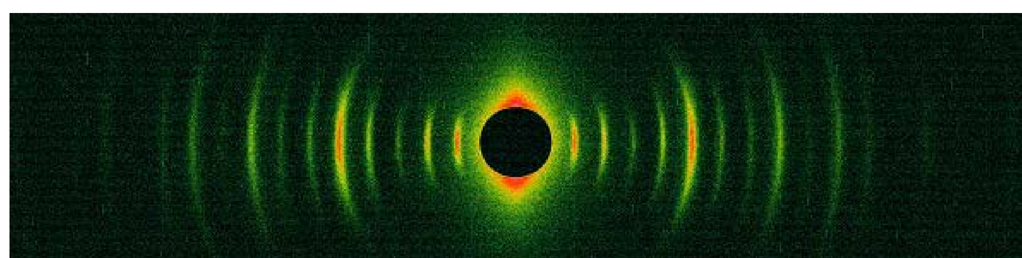


Concatenated image from lysozyme crystal using small DEPFET sensor 20x20μm^2

X-ray energy 12.4 keV
(wavelength=1.0Å)
@ BL-5A

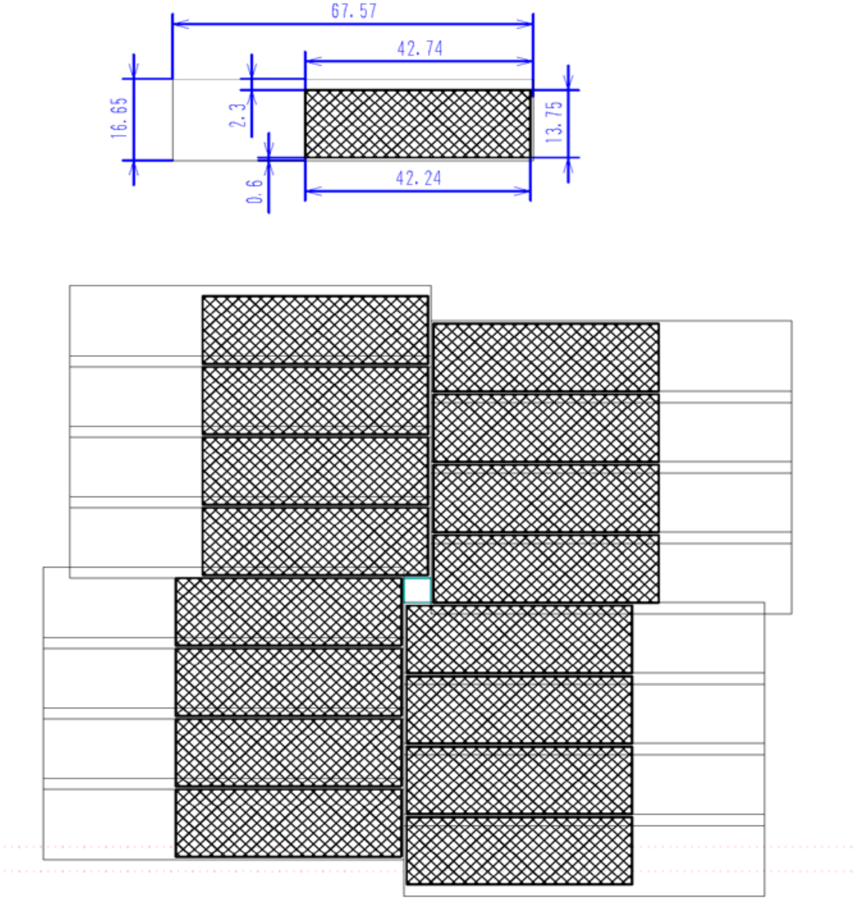
X-ray solution scattering image

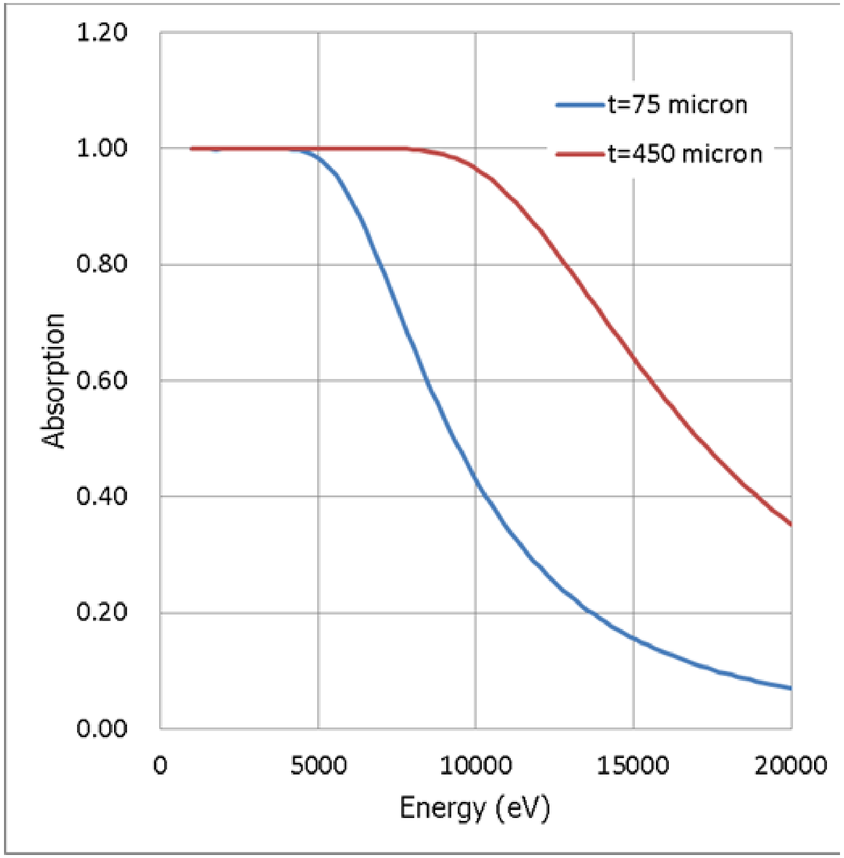
Collagen from Chicken Achilles tendon
o X-ray energy 8.33 keV (wave length=1.488Å)
@ BL-10C
o 1-dimentional orientation
o Lattice spacing: d=653Å



BELLE like sensors (20μs) for PF KEK

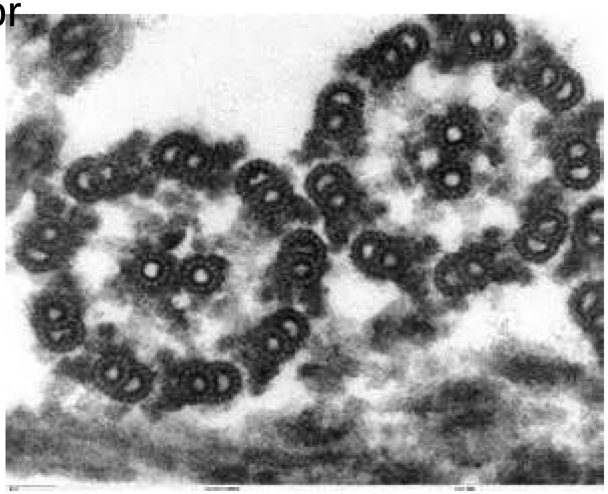
pixel size: 55 um x 55 um
number of rows and columns: 250 x 768





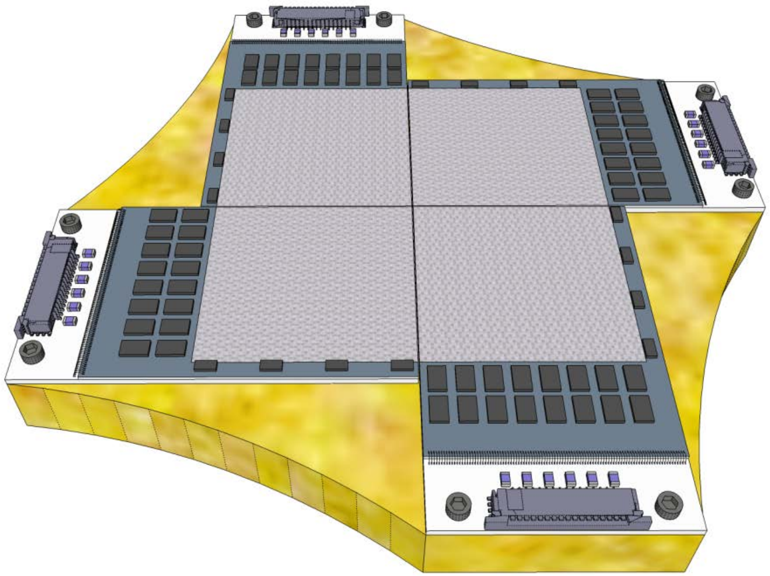
DEPFETs for low E electron detectors

Goal: develop high speed direct hit low energy electron detector
Solution: thin, nonlinear DEPFETs with 80kHz frame rate



- 1Mpix, 60µm DEPFET pixel, 4 quadrants, 6x6 cm² sensitive
- 50µm thin sensitive area
- Bidirectional 4-fold read out, frame rate: 80kHz
- memory to store ~100 frames

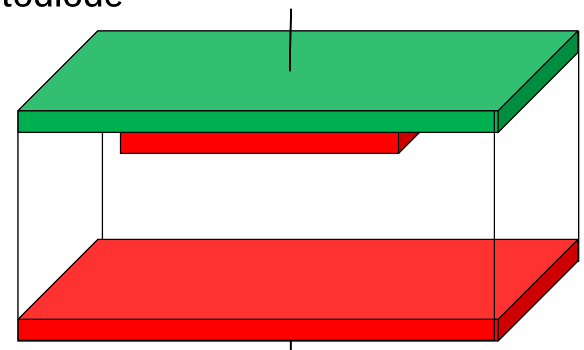
(collaboration partner MP Structural Dynamics)



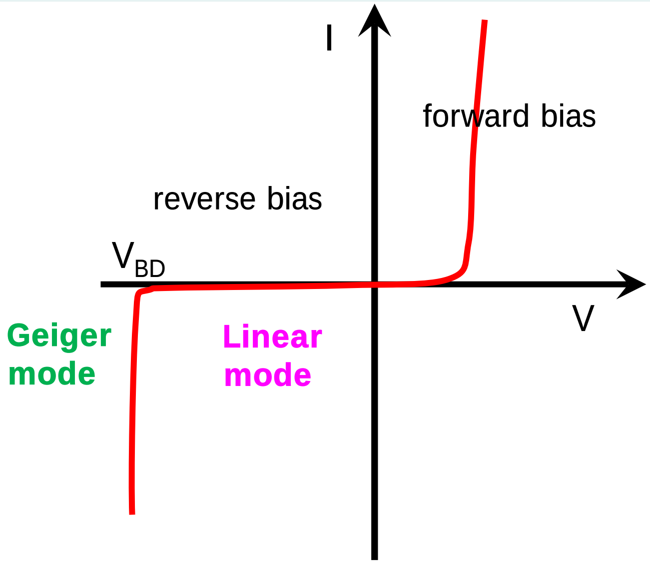
SNR improvements

- **Amplify signal**

Avalanche Photodiode

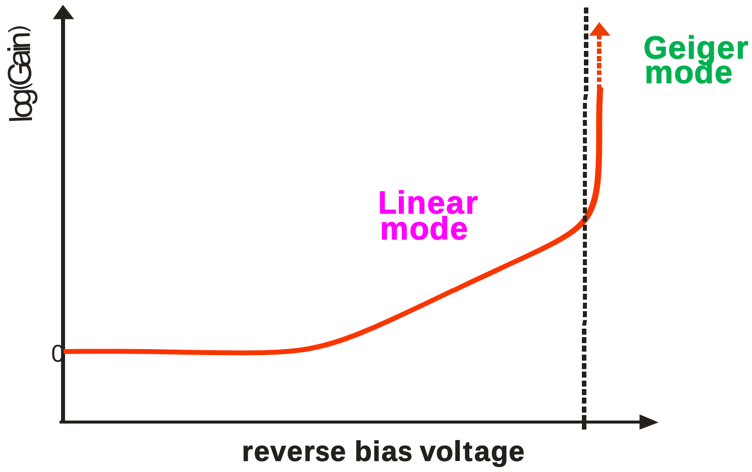


Avalanche photodiode



Linear / Proportional mode

Bias: slightly ***BELOW*** breakdown
Linear-mode: it's an ***AMPLIFIER***
Gain: limited < 300 (1000)



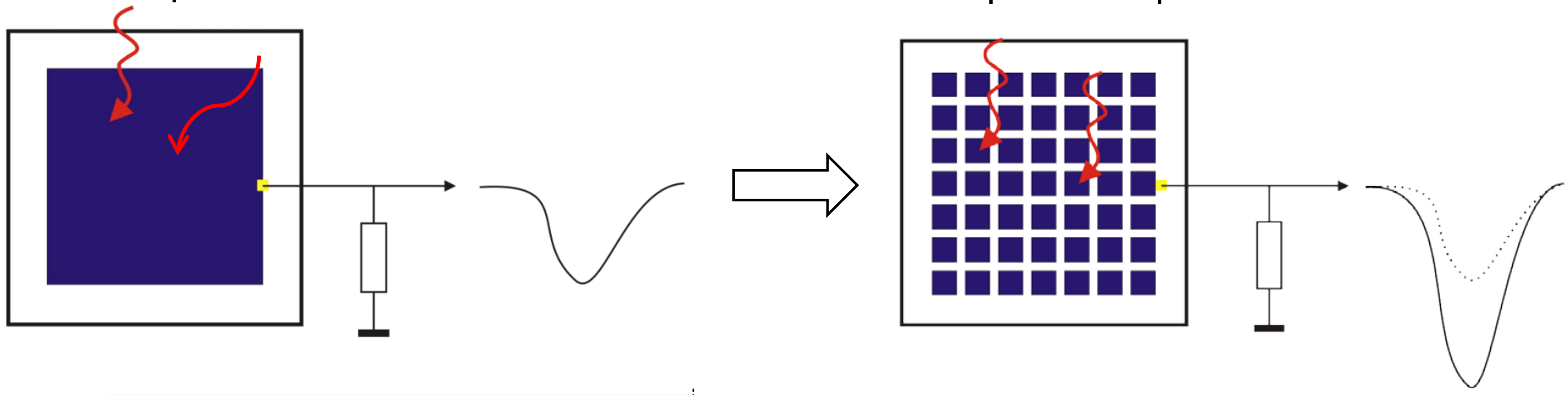
Geiger mode

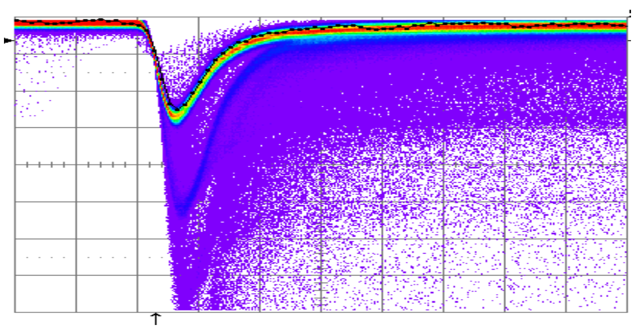
Bias: (10%-20%) ***ABOVE*** breakdown voltage
Geiger-mode: it's a ***BINARY*** device!!
Gain: **"***infinite***"** !!

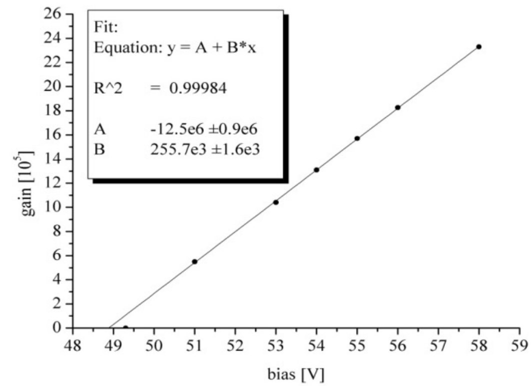
Silicon photomultiplier

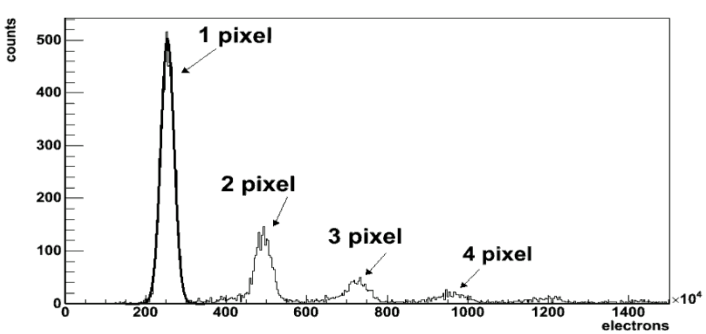
Avalanche photodiode

Silicon photomultiplier



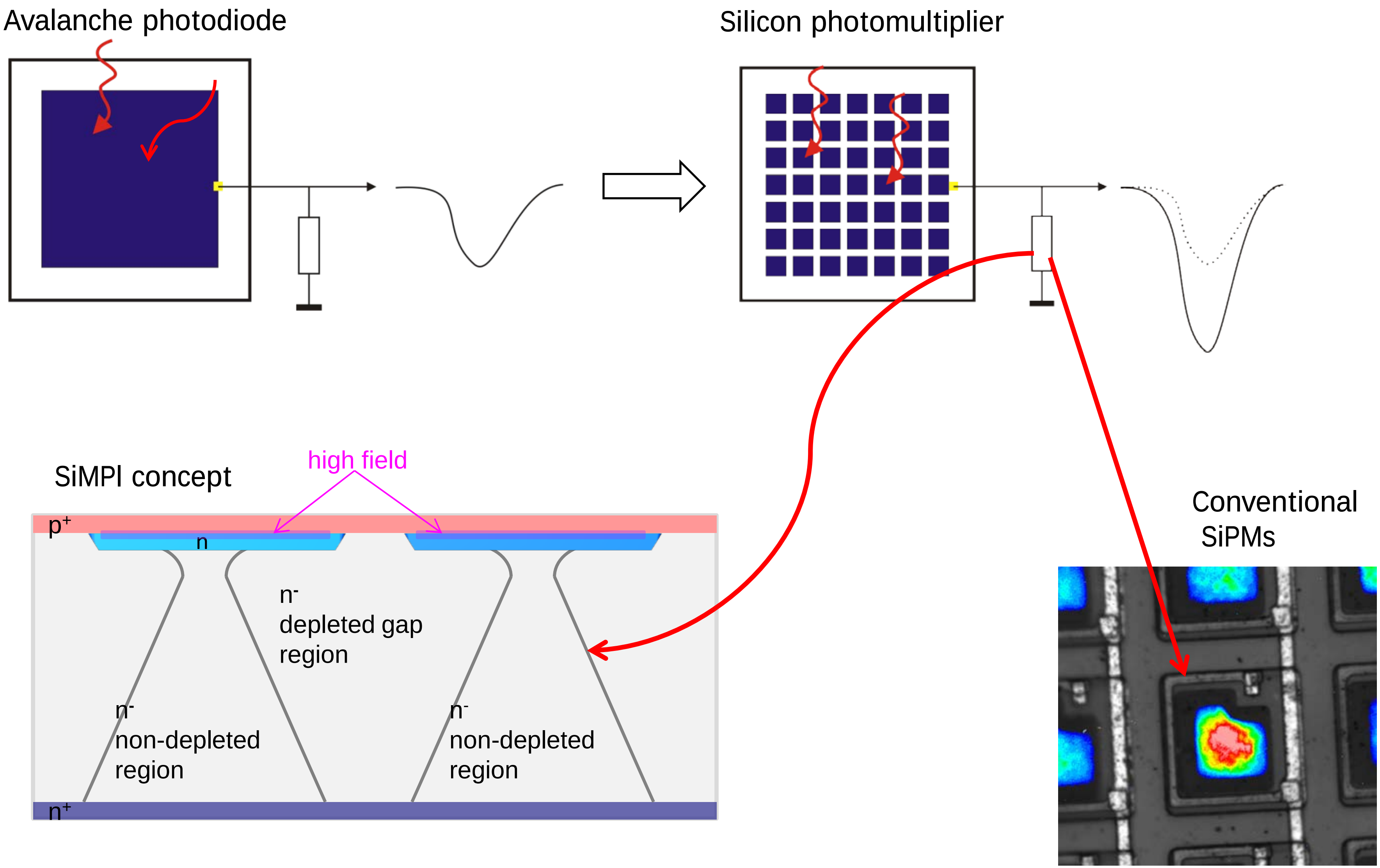




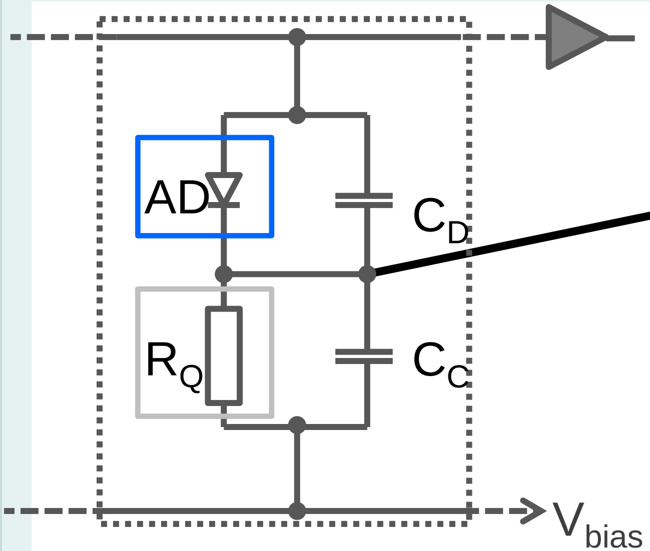


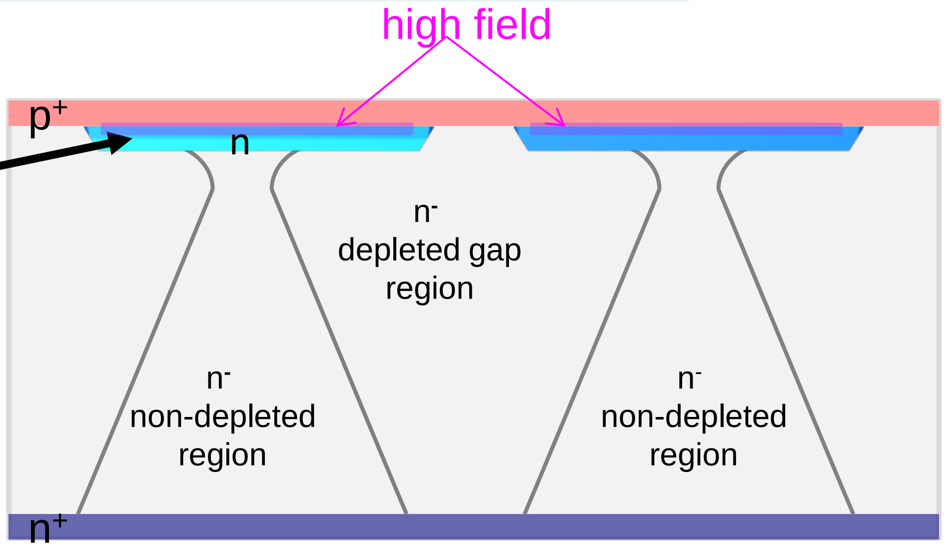
Operating voltage: «100 V
Gain: 10^5 up to 10^7
dependence of Gain on Temp.: 0.5% dG/dT

Silicon photomultiplier

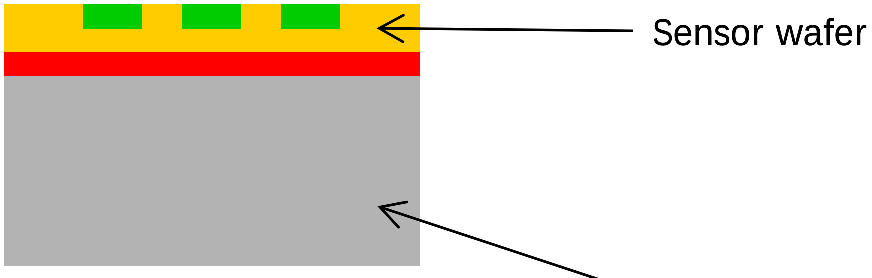


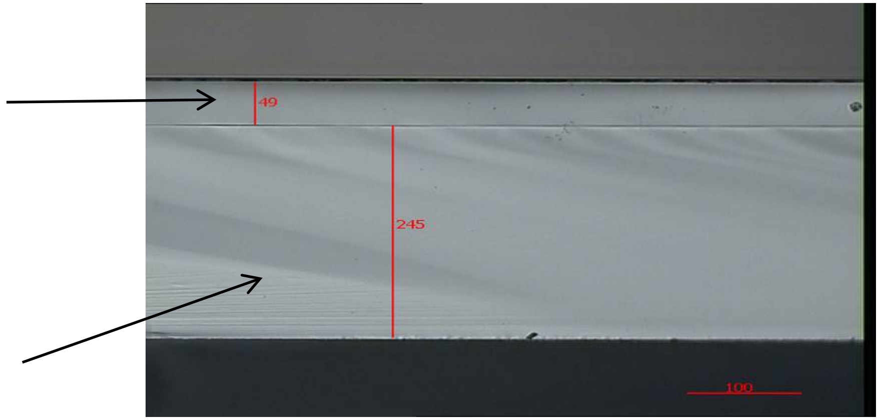
SiPM cell components → SiMPl approach





SOI wafers

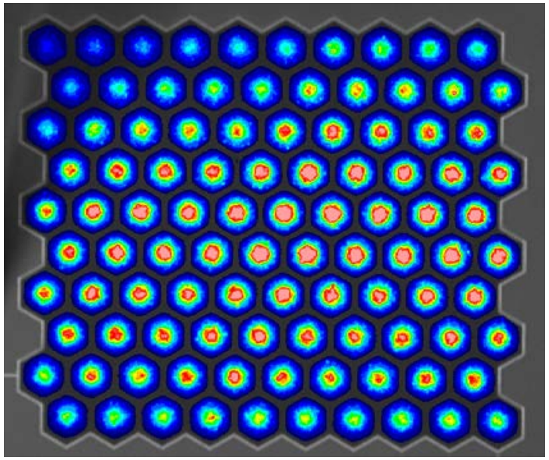




SiMPl : Advantages and Disadvantages

Advantages:

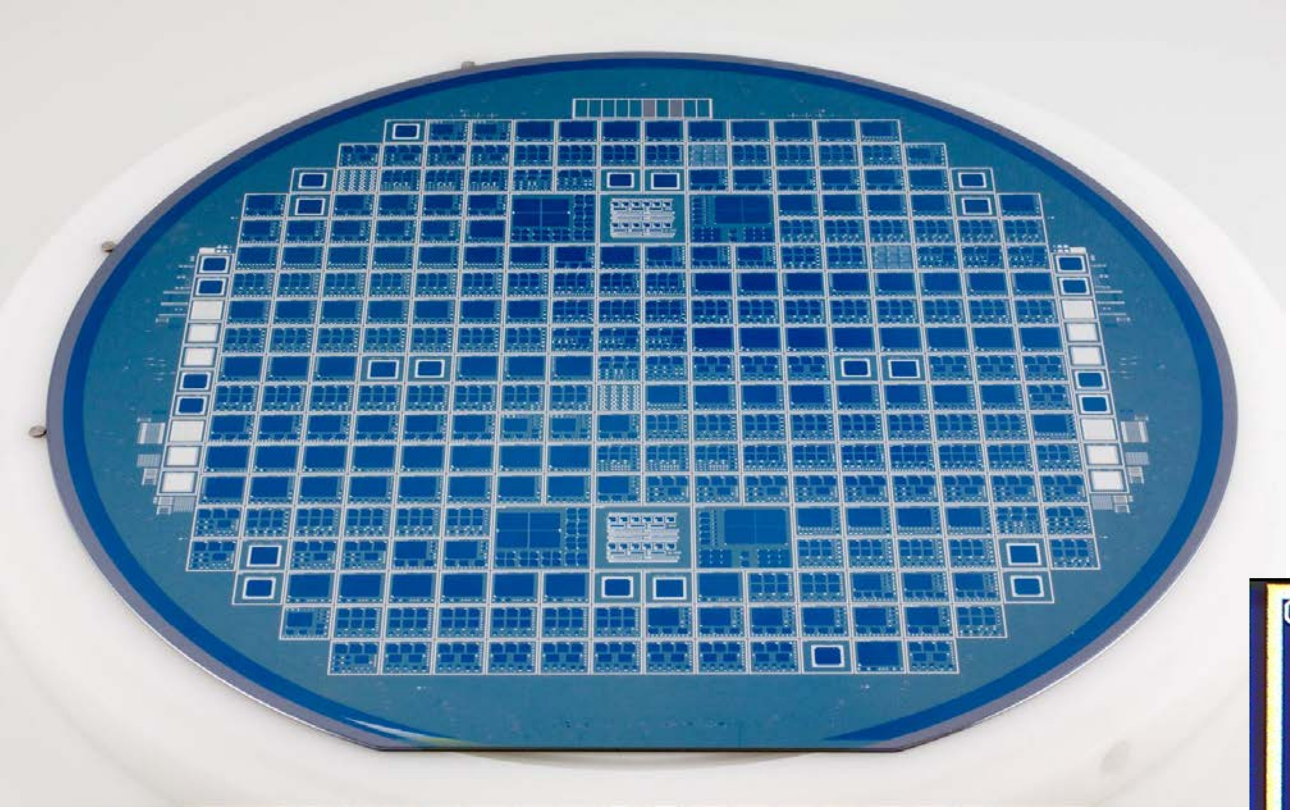
- no need of polysilicon
- free entrance window for light,
  no metal necessary within the array
- coarse lithographic level
- simple technology
- inherent diffusion barrier against minorities
  in the bulk → less optical cross talk

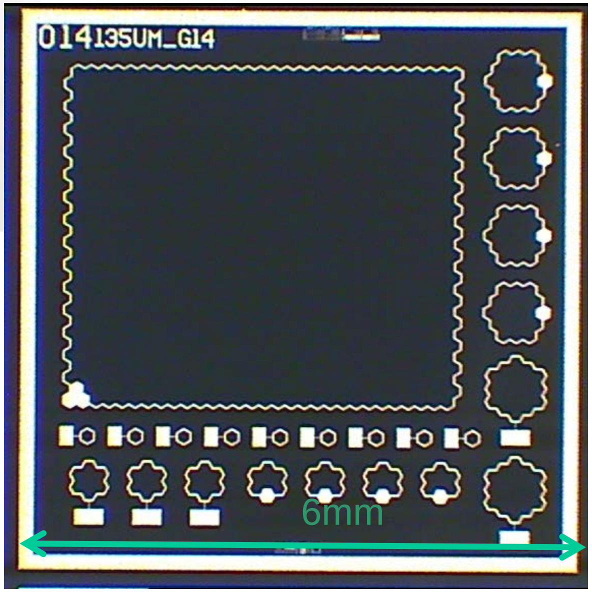


Drawbacks:

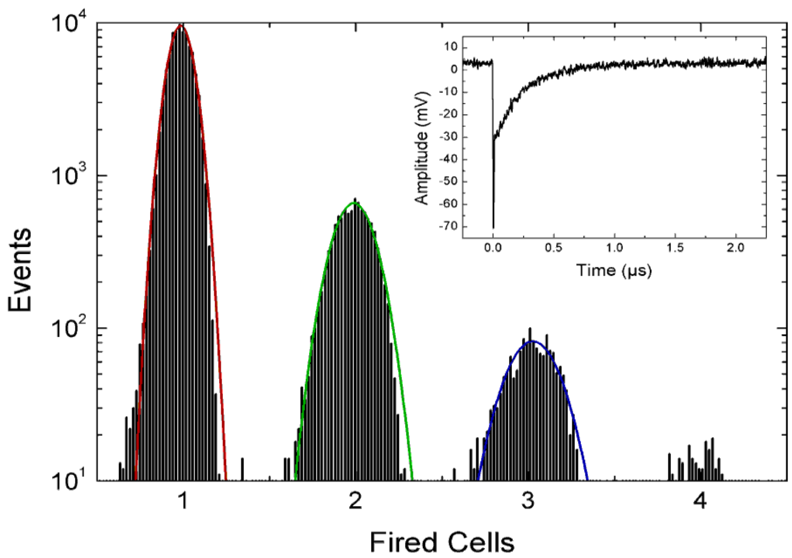
- required depth for vertical resistors does not match wafer thickness
- wafer bonding is necessary for big pixel sizes
- significant changes of cell size requires change of the material
- vertical ‘resistor‘ is a JFET → parabolic IV → longer recovery times

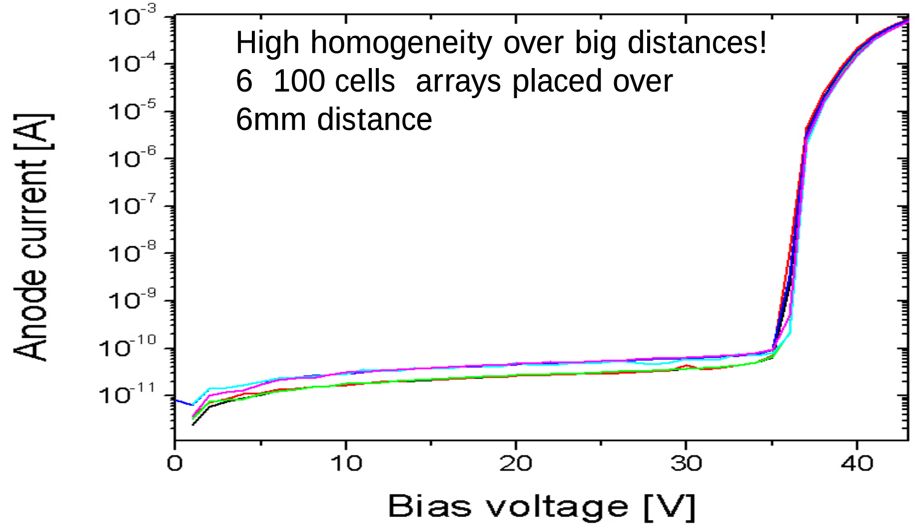
Prototype production

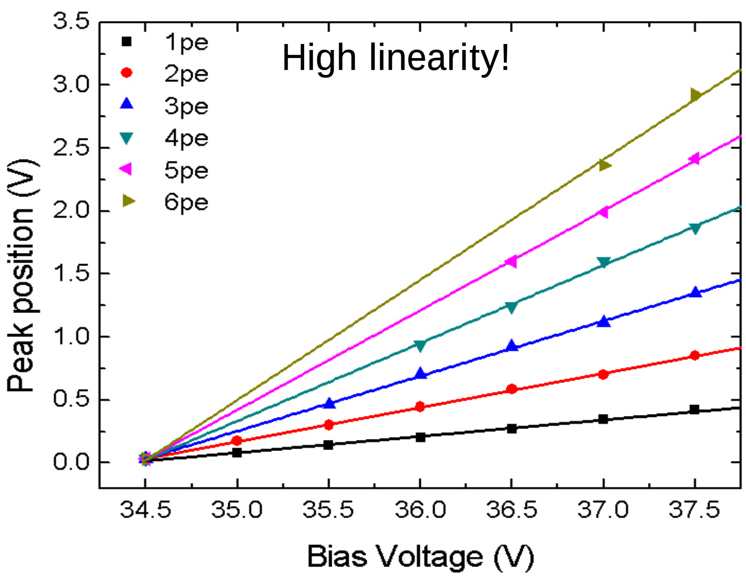


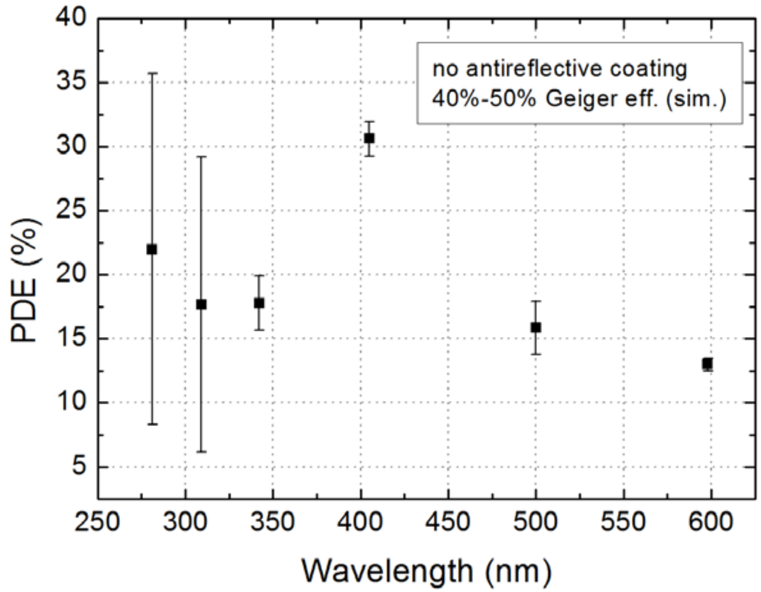


Prototype production







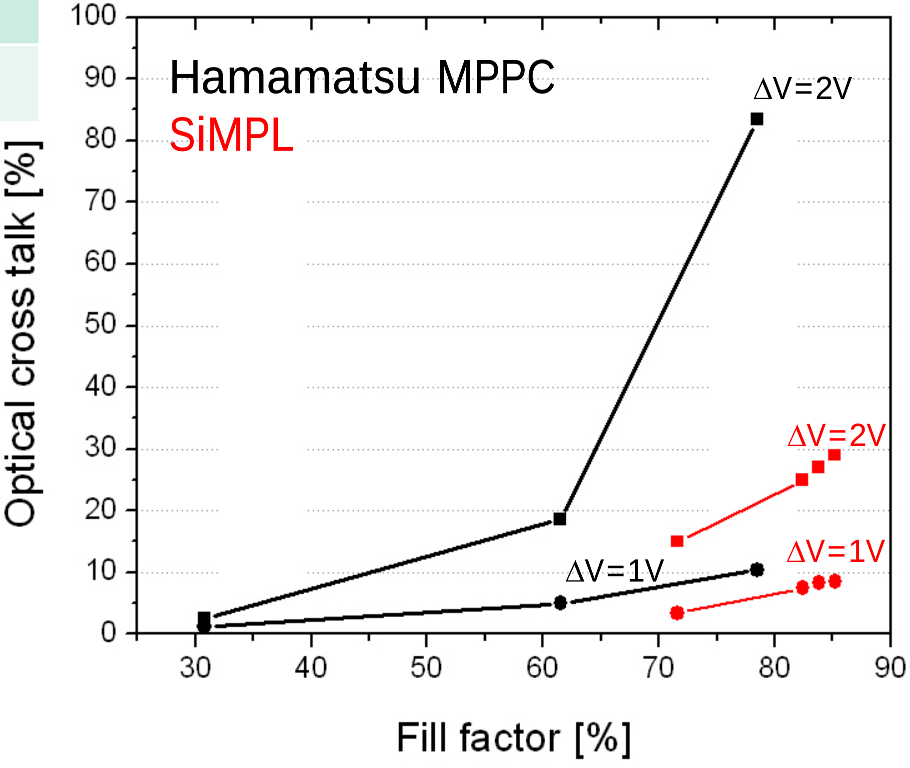


Fill factor & Cross Talk

Fill factor limited only by the cross talk suppression need!

Pitch / Gap	Fill factor	Cross talk meas. (ΔV=2V)
130μm / 10μm	85.2%	29%
130μm / 11μm	83.8%	27%
130μm / 12μm	82.4%	25%
130μm / 20μm	71.6%	15%

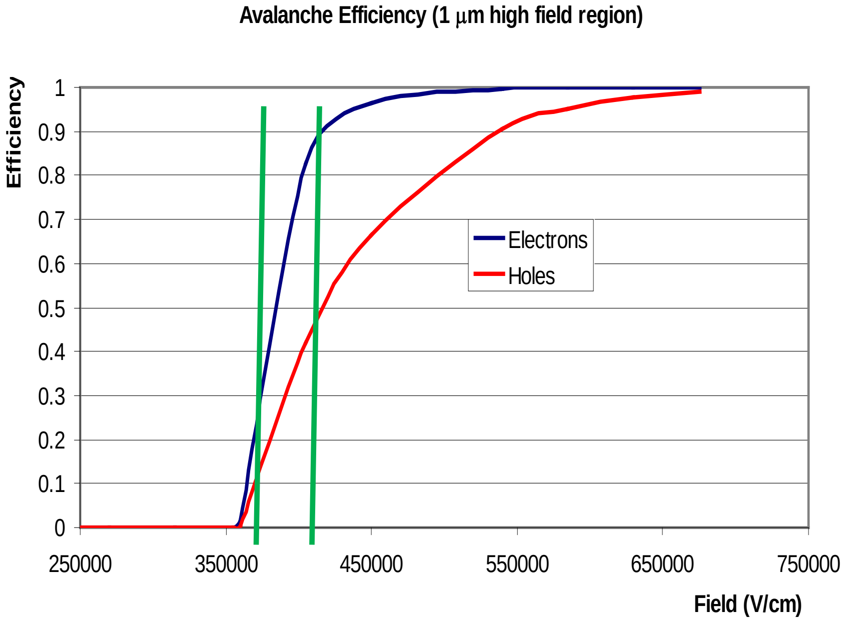
No special cross talk suppression technology applied just intrinsic property of SiMPl devices

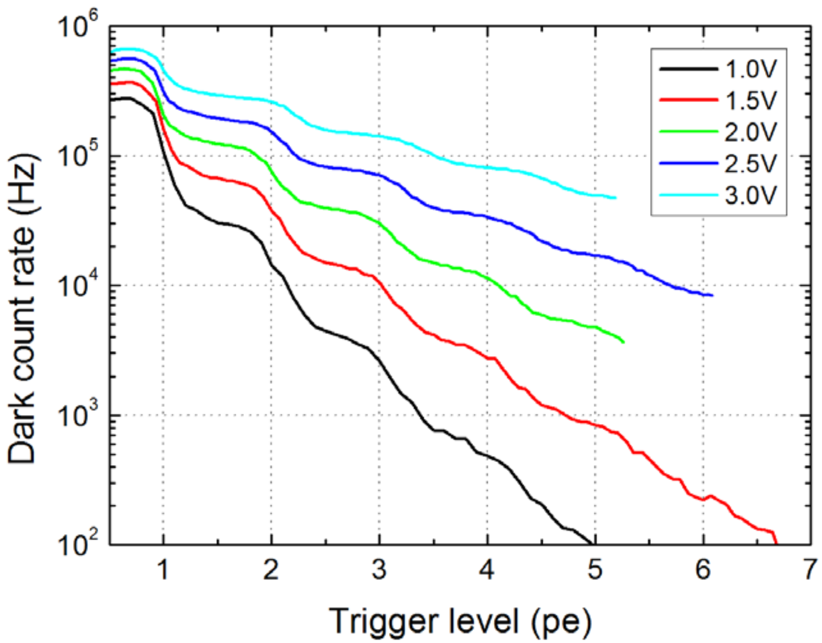


Detection of particles

Detection of particles:

- High gain in the sensor
- Excellent time stamping due to avalanche process (sub-ns)
- Minimum ionizing particles generate about 80 e-h-pairs/µm
- No need for high trigger efficiency

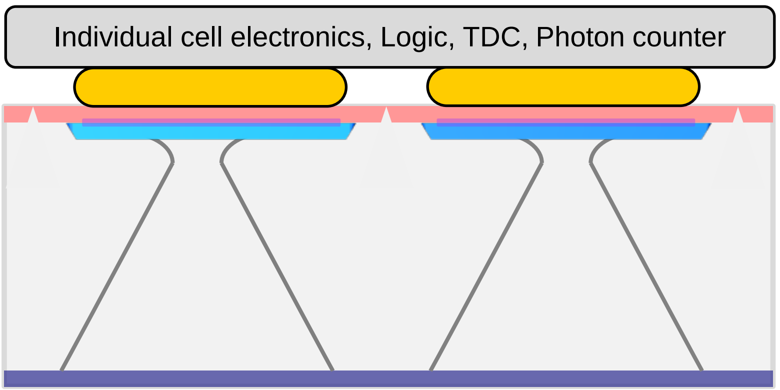




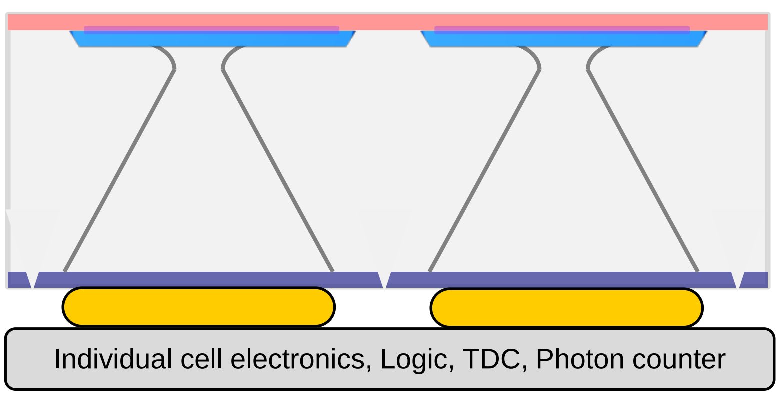
Reduction of dark rate and cross talk by order of magnitude

Next generation SiMPl devices - DSiPMI – collaboration with DESY

Ultra fast particle tracker - ***High energy physics application***



Ultra fast single photon sensitive imager – ***Photon science***



Sensor @ MPG HLL:

- Topologically flat surface
- High fill factor
- Adjustable resistor value
  Low RC -> very fast
- Single pixel readout
- Position sensitivity

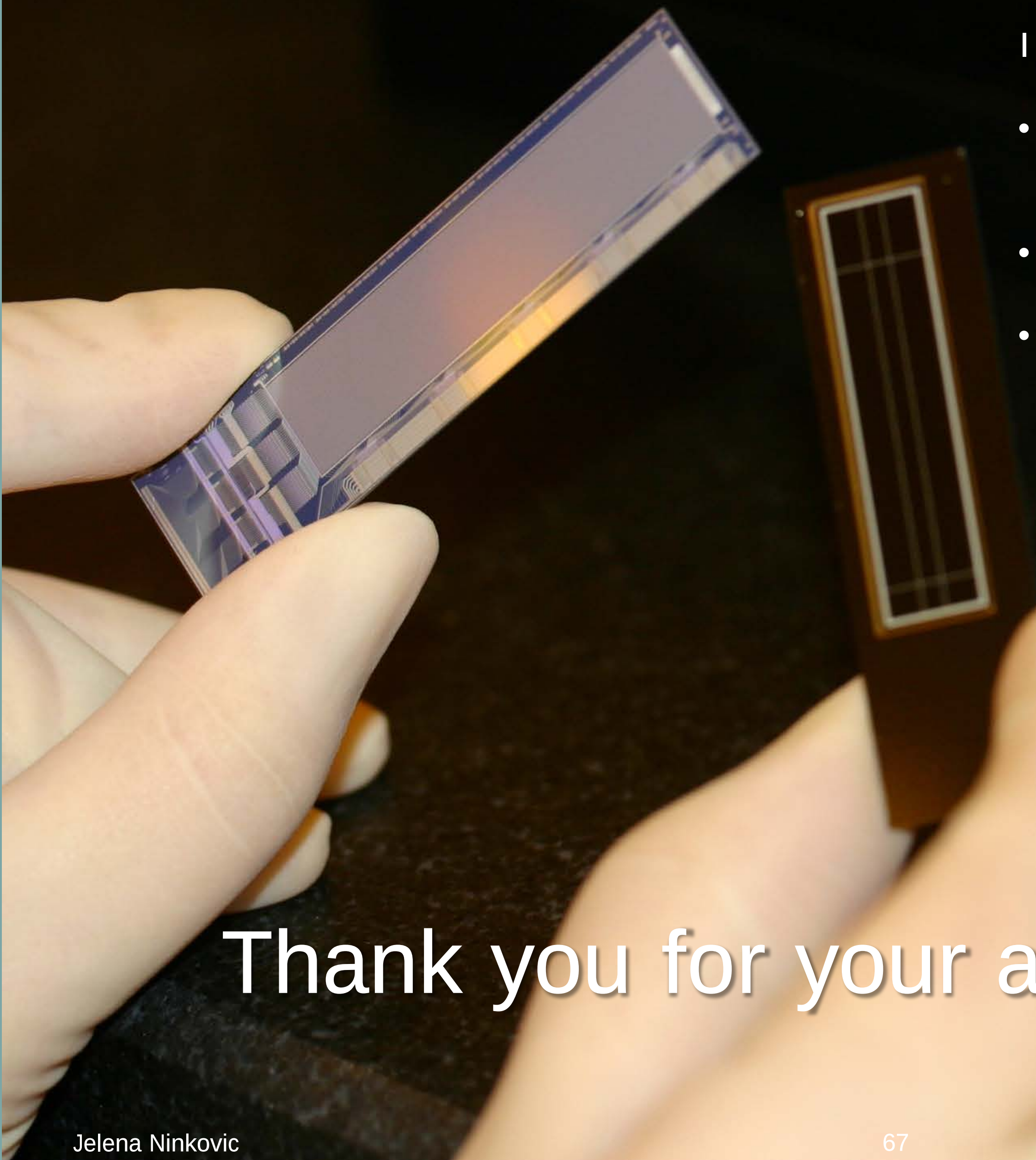
ASIC @ DESY:

- Active recharge
- Ability to turn off noisy pixels
- Fast timing
- Pitch limited by the bump bonding
- Position resolving signal processing

Possible applications:

- Future trackers at colliders
- Detectors for hadron therapies
- X ray detectors
- PET detectors
- Adaptive optic sensors

Summary



I showed :

- Some very attractive devices developed and produced at MPS Semiconductor Laboratory
  pnCCDs, DEPFETs , SiMPl ...
- Some of the potentials of those devices are used in current projects
- Still space to explore much more ...

Thank you for your attention ...